GD9Fx1G8F2D

DATASHEET

1G-bit 2K+128BPage Size

Contents

1. FEATURES

- Single level cell technology
- ONFI 1.0 Compatible
- Power Supply Voltage
  - VCC/VCCQ = 1.7 ~ 1.95v(GD9FS)
  - VCC/VCCQ = 2.7 ~ 3.6v (GD9FU)
- Memory Cell Organization
  - Page size:
  X8: 2K + 128bytes
  - Block size: 64 pages
  X8: 128K + 8K bytes
  - Plane size: 1024 blocks
  - Device size: 1024blocks
- Page Read / Program time
  - Random Read Time (tR): 25us Max.
  - Sequential Access Time
  3.3v Device: 12ns Min.
  1.8v Device: 20ns Min.
  - Page Program (tPROG): 300us Typ.
- Block Erase
  - Block Erase Time (tBERS): 3ms Typ.
- Operating Current
  - Read(Typ): 15mA
  - Program(Typ): 15mA
  - Erase(Typ): 15mA
  - Standby(Max):50uA (CMOS)
- Reliability
  - P/E cycles with ECC: 50K
  - Data retention: 10 Years
- ECC Requirement
  - 8bit/512 bytes
- Operating Temperature
  - Industrial: -40C ~ 85C
- Chip Enable Don't Care Option
- Security
  - UID
  - OTP Area
- Package
  - TSOP48 12mm x 20mm
  - FBGA63 9mm x 11mm
  - FBGA48 6mm x 8mm

2. GENERAL DESCRIPTION

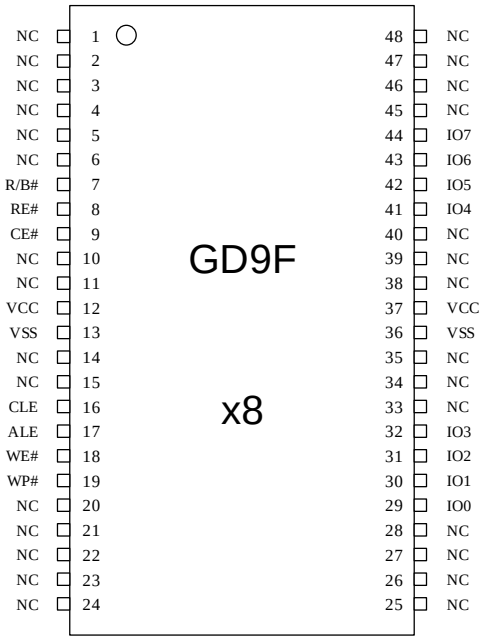
GigaDevice GD9Fx1G8F2D is 1Gbit capacity. A program operation can be performed in typical tPROG on each page and an erase operation can be performed in typical tBERS on each block. Data in the page can be read out at tRC cycle time per byte. The I/O pins serve as the ports for address and data input/output as well as command input. GD9Fx1G8F2D provides extended reliability of 50K program/erase cycles with ECC (Error Correcting Code).

2.1 Product List

PART NUMBER	ORGANIZATION	VCC RANGE	PACKAGE
GD9FS1G8F2DMGI	128M x 8bit	1.7v ~ 1.95v	TSOP(I)-48
GD9FS1G8F2DLGI	128M x 8bit	1.7v ~ 1.95v	FBGA63
GD9FS1G8F2DDGI	128M x 8bit	1.7v ~ 1.95v	FBGA48
GD9FU1G8F2DMGI	128M x 8bit	2.7v ~ 3.6v	TSOP(I)-48
GD9FU1G8F2DLGI	128M x 8bit	2.7v ~ 3.6v	FBGA63
GD9FU1G8F2DDGI	128M x 8bit	2.7v ~ 3.6v	FBGA48

3. PACKAGE

3.1 TSOPI-48



TOP View

Figure3- 1: TSOP48 x8 device package figures

3.2 FBGA-63

	1	2	3	4	5	6	7	8	9	10
A	NC	NC							NC	NC
B	NC								NC	NC
C			WP#	ALE	VSS	CE#	WE#	R/B#		
D			NC	RE#	CLE	NC	NC	NC		
E			NC	NC	NC	NC	NC	NC		
F			NC	NC	NC	NC	NC	NC		
G			NC	NC	NC	NC	NC	NC		
H			NC	IO0	NC	NC	NC	VCC		
J			NC	IO1	NC	VCC	IO5	IO7		
K			VSS	IO2	IO3	IO4	IO6	VSS		
L	NC	NC							NC	NC
M	NC	NC							NC	NC

TOP View

Figure3- 2: 63-FBGA x8 device ball location figures

3.3 FBGA-48

	1	2	3	4	5	6
A	WP#	ALE	VSS	CE#	WE#	R/B#
B	NC	RE#	CLE	NC	NC	NC
C	NC	NC	NC	NC	NC	NC
D	NC	NC	NC	NC	NC	NC
E	NC	NC	NC	NC	NC	NC
F	NC	IO0	NC	NC	NC	VCC
G	NC	IO1	NC	VCC	IO5	IO7
H	VSS	IO2	IO3	IO4	IO6	VSS

Figure 3-3: 48-FBGA x8 device ball location figures

4. BLOCK DIAGRAM

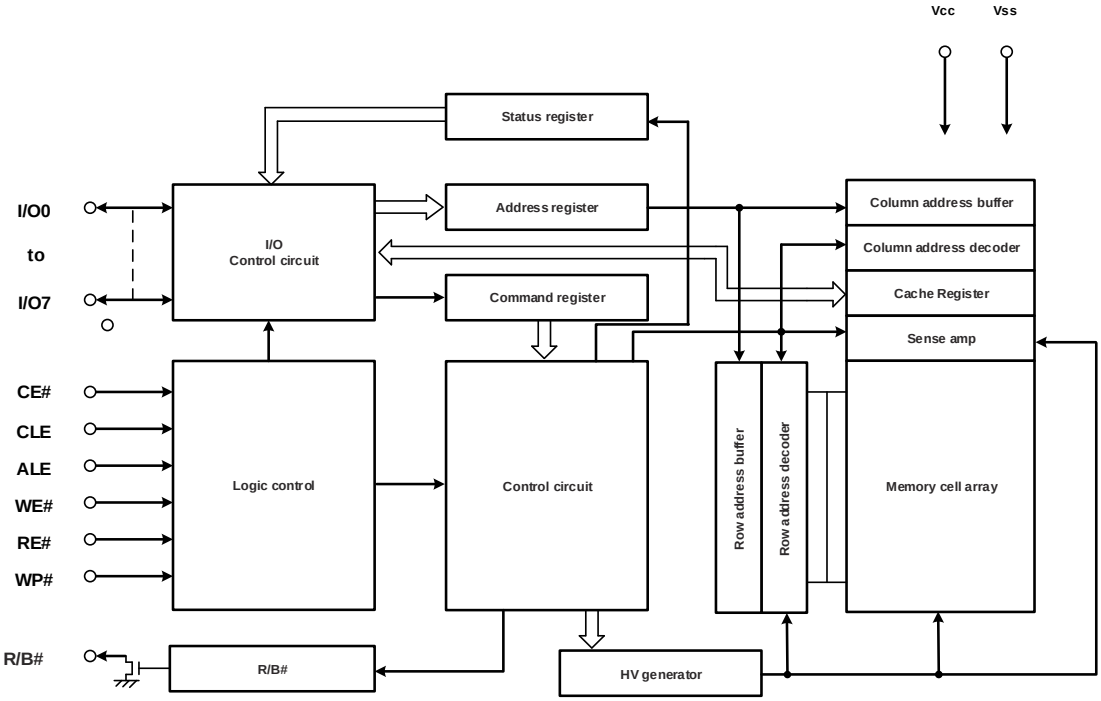


Figure 4-1: Block Diagram figures

PIN DESCRIPTION

Signal Name	Input/ Output	Description
R/B#	**O**	Ready/Busy：Open drain output to indicate the target status, low to indicate that one or more operations are in progress.
RE#	**I**	Read Enable：Enables serial data output, active low.
CE#	**I**	Chip Enable：When high and the target is in the ready state, the target goes into a low-power standby state. When low, the target is selected.
CLE	**I**	Command Latch Enable：Enable signal to load a command into the target on the rising edge of WE#, active high.
ALE	**I**	Address Latch Enable：Enable signal to load an address into the target on the rising edge of WE#, active high.
WE#	**I**	Write Enable：Data, Commands, and Addresses are latched on the rising edge of WE#.
WP#	**I**	Write Protect：Low to disable Flash array program and erase operations.
IO0 ~ IO7	**I/O**	I/O Port, bits 0-7：8-bit wide bidirectional port for transferring address, command, and data to and from the device.
VCC	**I**	Power：Power supply to the device.
VSS	**I**	Ground：Power supply ground.
NC	**-**	No Connection：Lead is not internally connected.

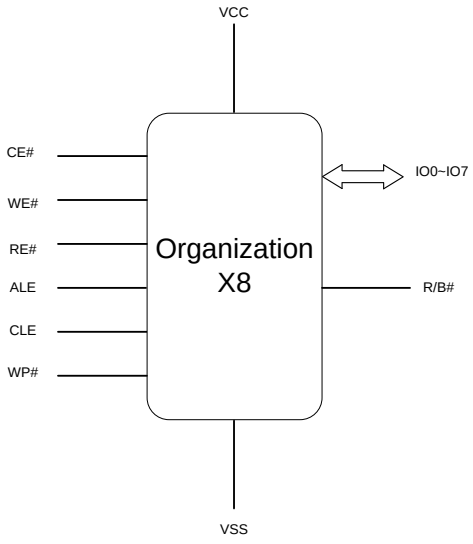


Figure 4-2: x8 device figures

5. ARRAY ORGANIZATION

Each device has	Each block has	Each page has	
1G			
128M+8M	128K+8K	2K+128	bytes
1024 x 64	64	-	pages
1024	-	-	blocks

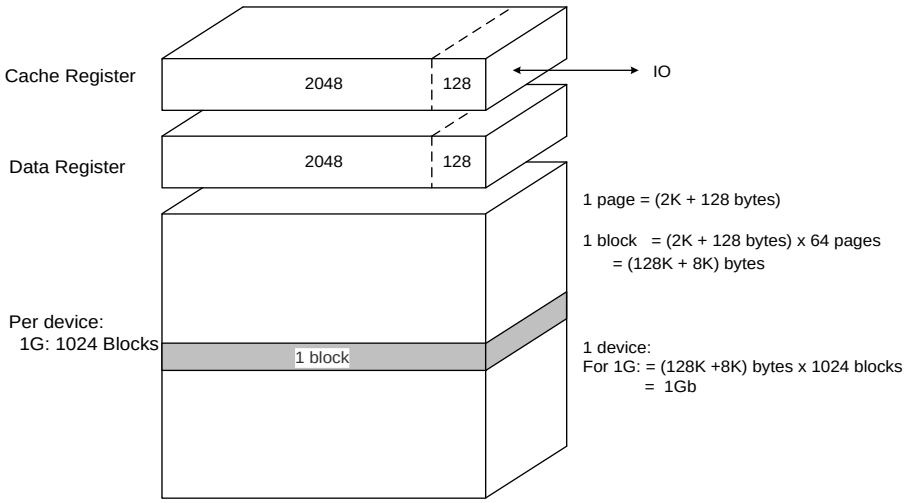


Figure 5-1: Array Organization figures

5.1 Addressing (X8)

Bus Cycle	IO0	IO1	IO2	IO3	IO4	IO5	IO6	IO7
1st Cycle	A0	A1	A2	A3	A4	A5	A6	A7
2nd Cycle	A8	A9	A10	A11	L	L	L	L
3rd Cycle	A12	A13	A14	A15	A16	A17	A18	A19
4th Cycle	A20	A21	A22	A23	A24	A25	A26	A27

A0-A11: column address in the page
A12-A17: page address in the block
A18-A27: block address

5.2 Factory Defect Mapping

The Flash array is not presumed to be pristine, and a number of defects that makes the blocks unusable may be present. Invalid blocks shall be sorted out from normal blocks by software.

5.2.1. Device Requirements

If a block is defective, the manufacturer shall mark the block as defective by setting the Defective Block Marking, as shown in Figure of “Area marked in first or last page of block indicating defect”, of the last page of the defective block to a value of non-FFh. The Defective Block Marking is located on the first byte of user data area or the first byte of spare data area in the pages within a block.

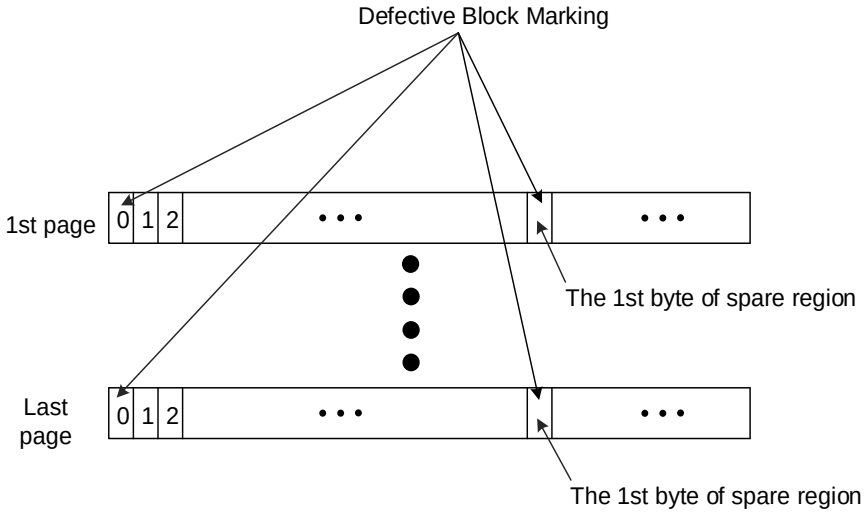


Figure 5-2: area marked in first or last page of block indicating defect sequential figures

5.2.2. Host Requirements

The host shall not erase or program blocks marked as defective by the manufacturer, and any attempt to do so yields indeterminate results.

Figure of “Flow chart to create initial invalid block table” outlines the flow chart how to create an initial invalid block table. It should be performed by the host to create the initial bad block table prior to performing any erase or programming operations on the target. The 1st byte of both main and spare region in non-defective blocks are read FFh with ECC enabled on the controller. A defective block is indicated by the majority of bits being read non-FFh in the Defective Block Marking location of either the first page or last page of the block. The host shall check the Defective Block Marking location of both the first and last past page of each block to verify the block is valid prior to any erase or program operations on that block.

NOTE: Over the lifetime use of a NAND device, the Defective Block Marking of defective blocks may encounter read disturbs that cause bit changes. The initial defect marks by the manufacturer may change value over the lifetime of the device, and are expected to be read by the host and used to create a bad block table during initial use of the part.

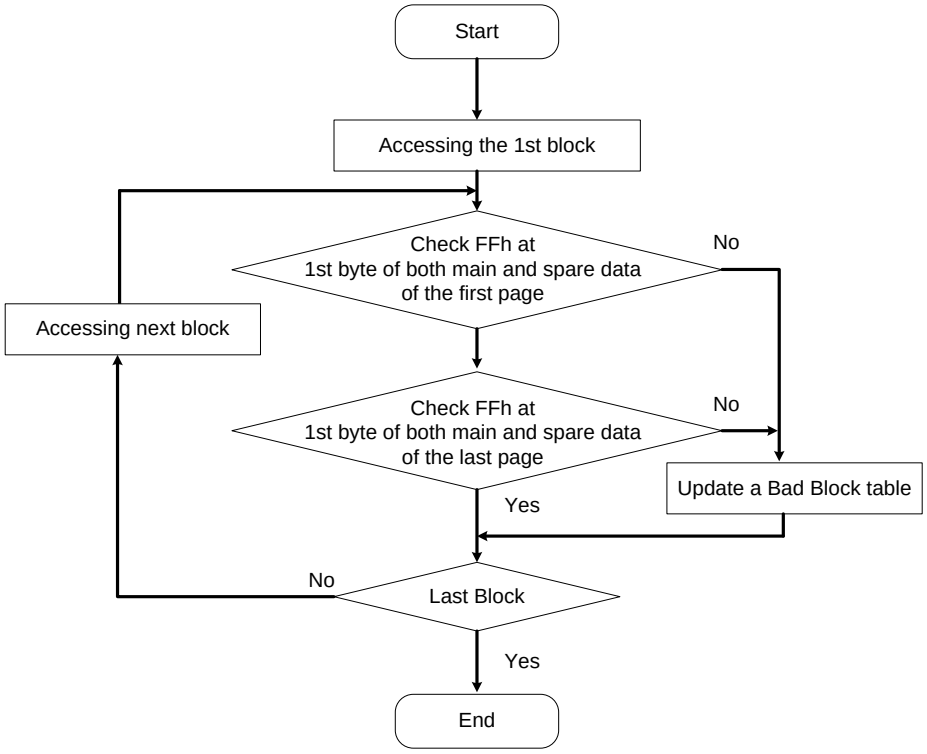


Figure 5-3: flow chart to create initial invalid block table sequential figures

6. COMMAND SET

Function	1st	2nd	3rd	4th	During busy
Page read	00H	30H	--	--	No
Read for copy-back	00H	35H	--	--	No
Random data output(change column address)	05H	E0H	--	--	No
Cache read start	31H	--	--	--	No
Cache read random	00H	31H	--	--	No
Cache read end	3FH	--	--	--	No
Read id	90H	--	--	--	No
Read status register	70H	--	--	--	Yes
Page program start / Cache program end	80H	10H	--	--	No
Random data input	85H	--	--	--	No
Copy back program	85H	10H	--	--	No
Cache program start	80H	15H	--	--	No
Block erase	60H	D0H	--	--	No
Reset	FFH	--	--	--	Yes
Read parameter page	ECH	--	--	--	No
Read unique ID	EDH	--	--	--	No
Get Features	EEH	--	--	--	No
Set Features	EFH	--	--	--	No

7. BUS OPERATION

The bus on the device is multiplexed. Data I/O, addresses, and commands all share the same pins.

The command sequence typically consists of a COMMAND LATCH cycle, address input cycles, and one or more data cycles, either READ or WRITE.

There are several standard bus operations that control the device. These are Command Input, Address Input, Data Input, Data Output, Write Protect, and Standby.

CLE	ALE	CE#	WE#	RE#	WP#	MODE
H	L	L	Rising	H	X	Command input for read mode
L	H	L	Rising	H	X	Address input for read mode
H	L	L	Rising	H	H	Command input for write mode
L	H	L	Rising	H	H	Address input for write mode
L	L	L	Rising	H	H	Data input
L	L	L	H	Falling	X	Sequential read and data output
L	L	X	H	H	X	During read(busy)
X	X	X	X	X	H	During program/Erase(busy)
X	X	X	X	X	L	Write protect
X	X	H	X	X	0V / VCC	Standby

Notes:

1. X can be VIL or VIH. H = Logic level HIGH. L = Logic level LOW.
2. WP# should be biased to CMOS high or CMOS low for stand-by mode.
3. WE# and RE# during Read Busy must be keep on high to prevent unplanned command/address/data input or to avert unintended data out. In this time, only Reset and Read Status can be input to the device.

7.1 Command Input Cycle

Command Input bus operation is used to give a command to the memory device. Commands are accepted with Chip Enable Low, Command Latch Enable High, Address Latch Enable Low and Read Enable High and latched on the rising edge of Write Enable. Moreover, for commands that starts a modify operation (write/erase) the Write Protect pin must be high.

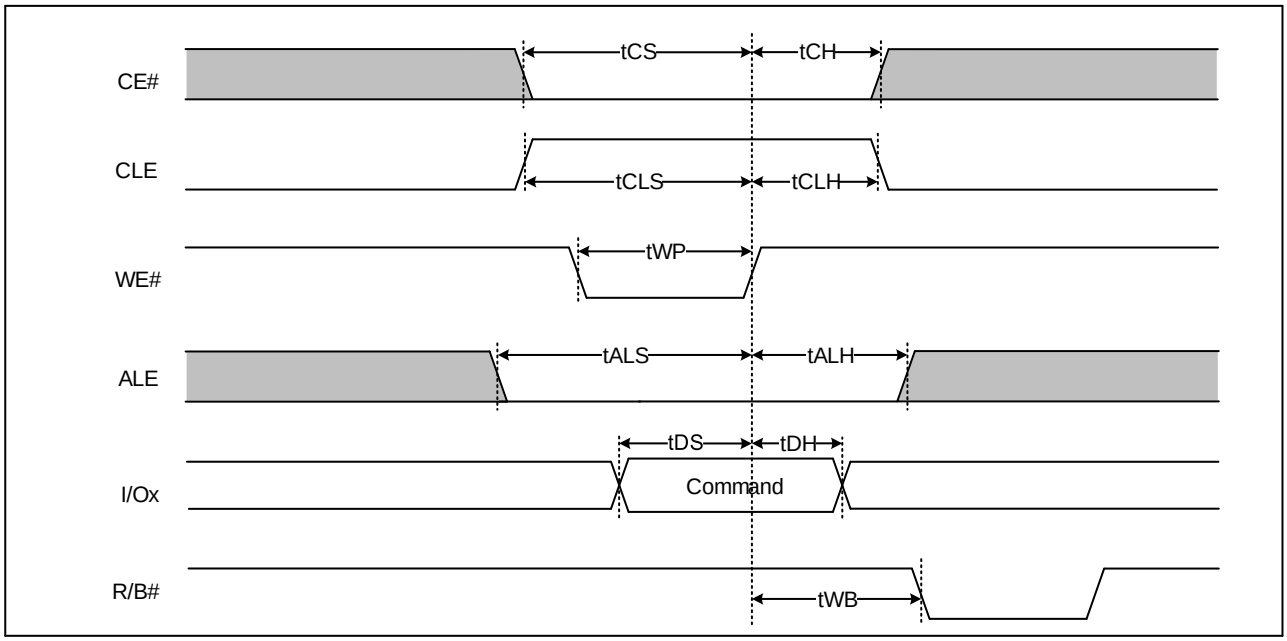


Figure 7-1: Command Input Cycle figures

7.2 Address Input Cycle

Address Input bus operation allows the insertion of the memory address. Addresses are accepted with Chip Enable Low, Address Latch Enable High, Command Latch Enable Low and Read Enable High and latched on the rising edge of Write Enable. Moreover, for commands that starts a modify operation (write/erase) the Write Protect pin must be high.

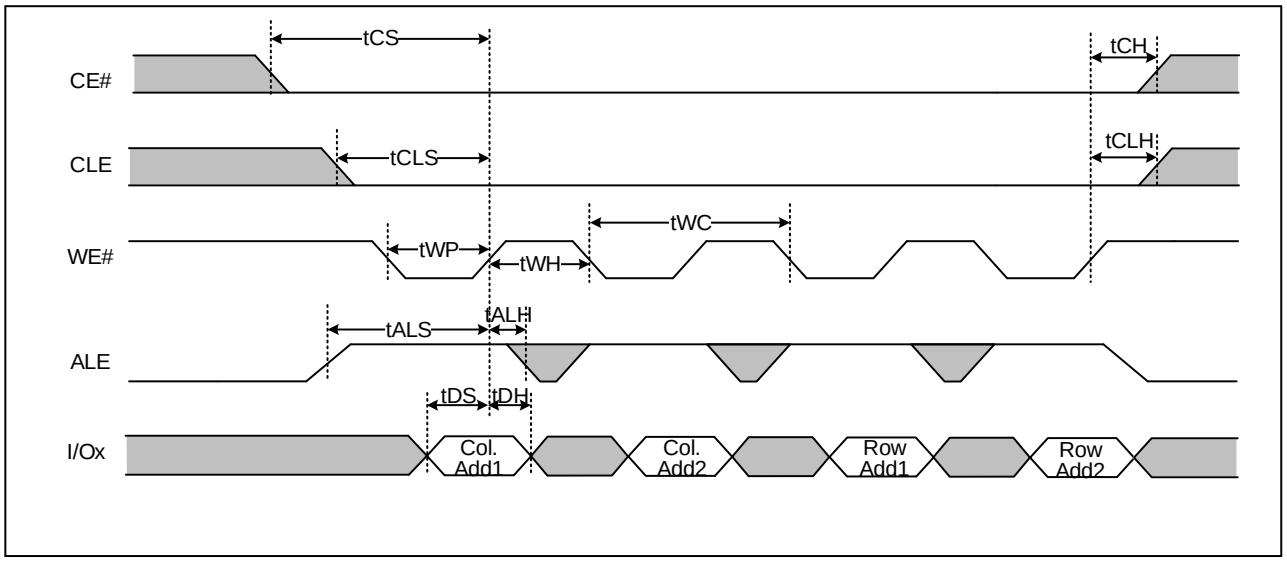


Figure 7-2: Address Input Cycle figures

7.3 Data Input Cycle

Data Input bus operation allows to feed to the device the data to be programmed. The data insertion is serially and timed by the Write Enable cycles. Data are accepted only with Chip Enable Low, Address Latch Enable Low, Command Latch Enable Low, Read Enable High, and Write Protect High and latched on the rising edge of Write Enable.

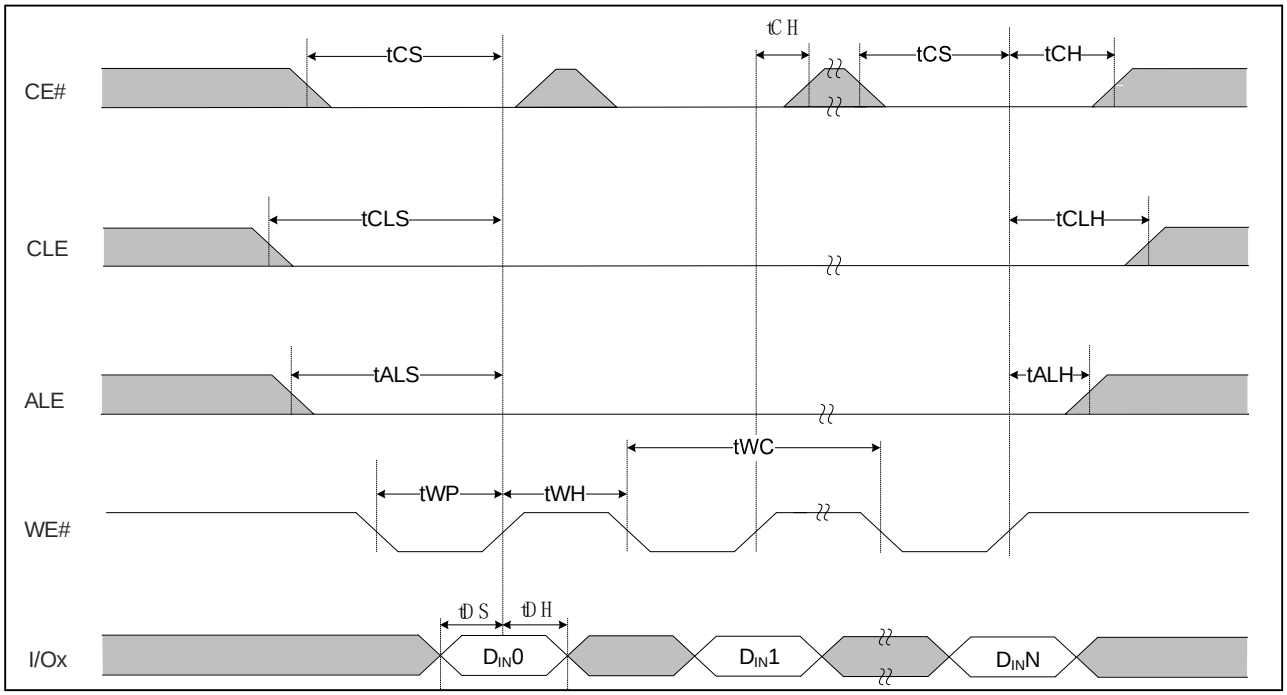


Figure 7-3: Data Input Cycle figures

7.4 Data Output Cycle

Data Output bus operation allows to output data from the device. The data output cycle is serially and timed by the Read Enable cycles. Data output may be used with CE# don't care. However, if CE# don't care is used tCEA and tCOH timing requirements shall be met by the host.

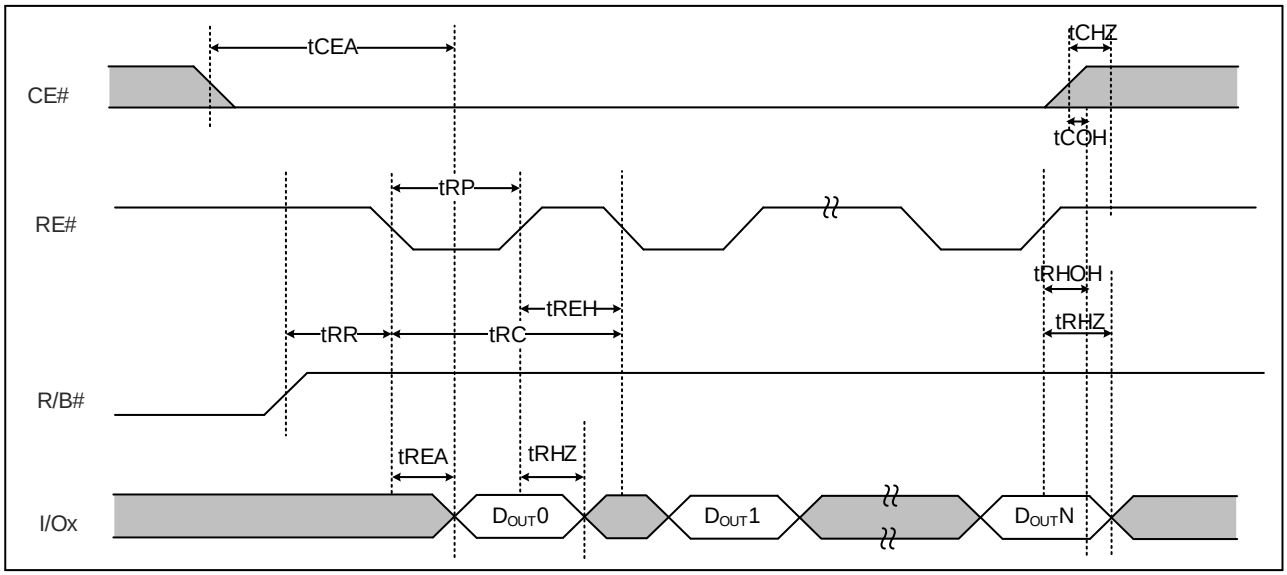


Figure 7-4_a: Data Output Cycle figures

If the host side uses a sequential access time (tRC) of less than 30ns, the data can be latched on the next falling edge of RE# as the waveform of EDO (Extended data output) mode.

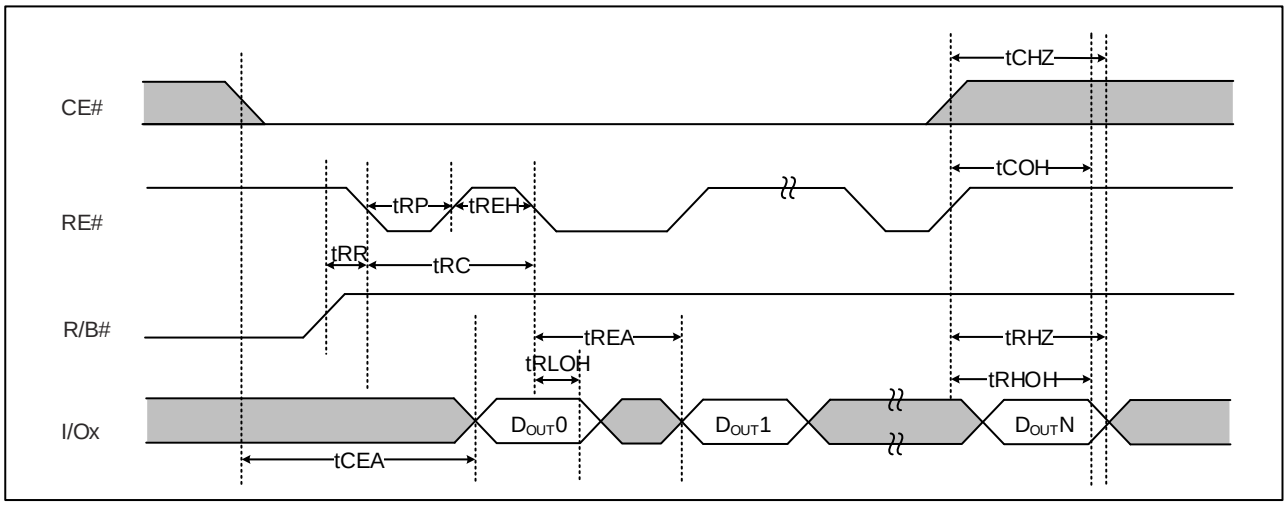


Figure 7-4_b: Data Output Cycle figures

7.5 Write Protect

The Erase and Program Operations are automatically reset when WP# goes Low. The operations are enabled and disabled as follows.

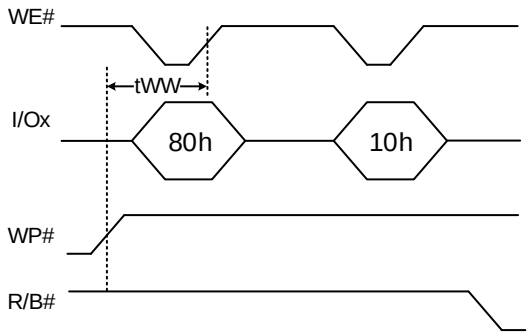


Figure7-5_a: Write Protect Disable with program figures

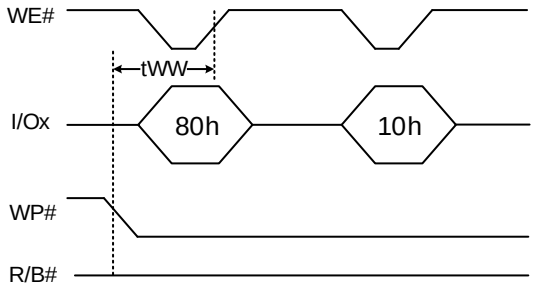


Figure 7-5_b: Write Protect Enable with program figures

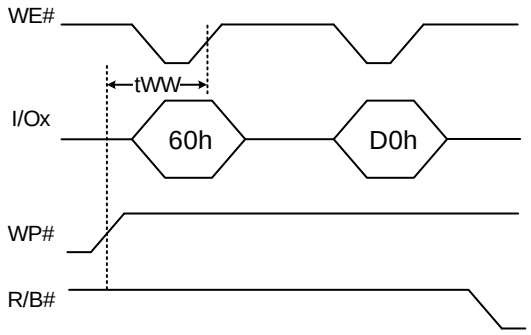


Figure 7-5_c: Write Protect Disable with erase figures

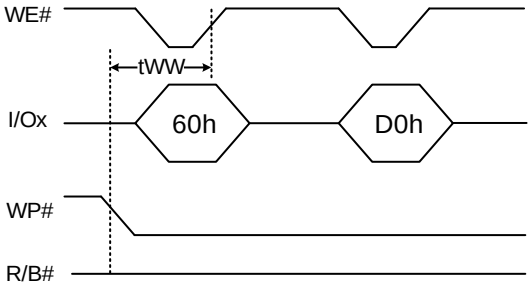


Figure 7-5_d: Write Protect Enable with erase figures

8. OPERATION DESCRIPTION

8.1 Page Read Operation

8.1.1 Common Page Read (00H-30H)

Read is initiated by writing 00H-30H to the command register along with four address cycles. The system controller can detect the completion of this data transfer (tR) by analyzing the output of R/B# pin or read status command. Once the data in a page is loaded into the cache register, they may be read out in tRC by sequentially toggle RE#. The repetitive high to low transitions of the RE# clock make the device output the data starting from the selected column address up to the last column address.

After the last data has been read out, CE# may be pulled up for some time to end the read operation, while during the RE# toggle cycle, CE# may be don't care when RE# is high. The CE# Don't Care feature may simplify the system interface, which allows controller to download the code from flash device directly, and the CE# transitions will not stop the read operation during the latency time.

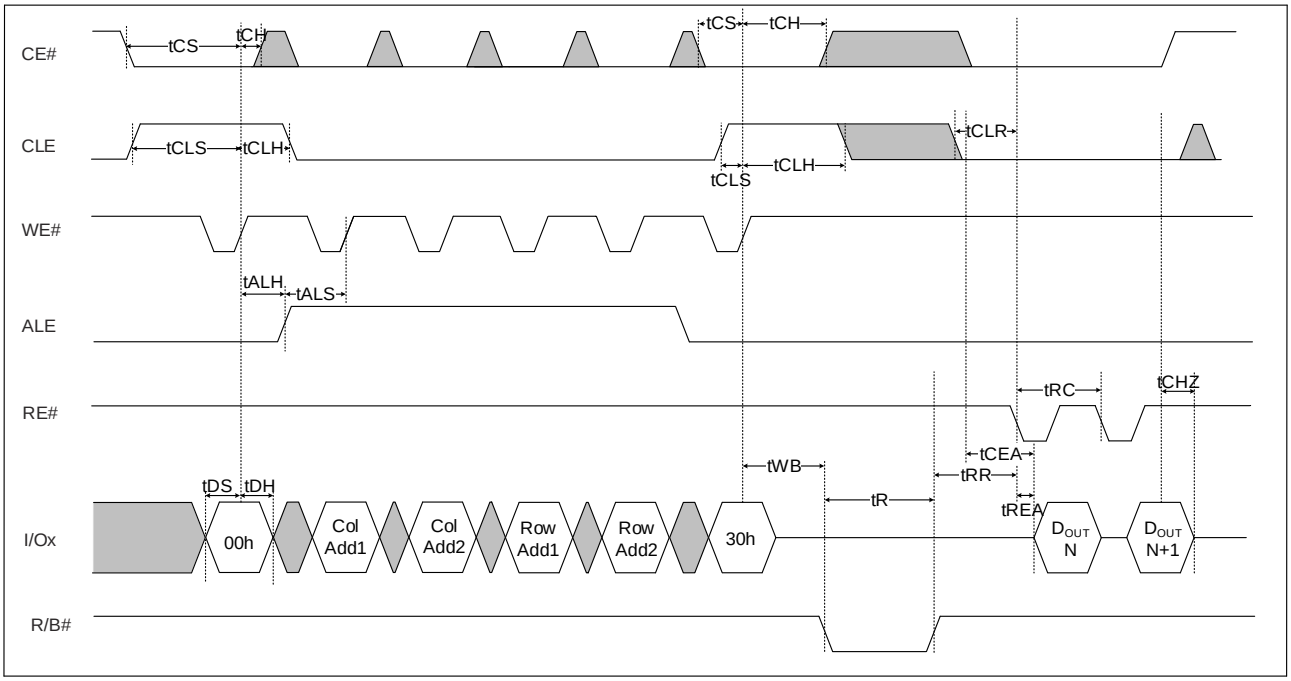


Figure 8-1: Common Page Read figures

8.1.2 Random Data Output (05H-E0H)

The device may output random data in a page instead of the consecutive sequential data by input random data output command (05H-E0H). The column address of next data, which is going to be out, may be changed to the address which follows random data output command. Random data output can be operated multiple times regardless of how many times it is done in a page, Random data output shall only be issued when the device is in a read idle condition.

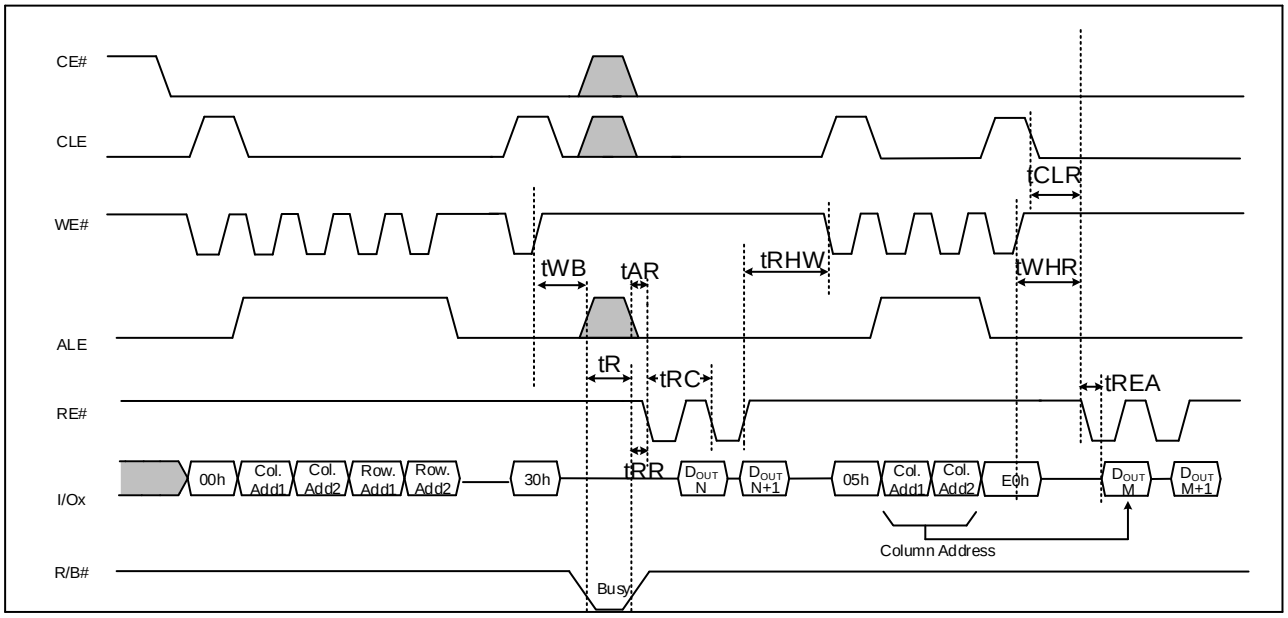


Figure 8-2: Random Data Output figures

Note: the address followed 05h can be only 2bytes cycle.

8.1.3 Cache Read Operation (31H/3FH)

The Cache Read function permits a page to be read from the cache register while another page is simultaneously read from the Flash array, and is available only within a block. A Read Page command shall be issued prior to the initial sequential or random Read Cache command in a read cache sequence. A Read Cache command shall be issued prior to a Read Cache End (3FH) command being issued.

The Cache Read function may be issued after the read function is completed. The host may enter the address of the next page to be read from the Flash array. Data output always begins at column address 00H. If the host does not enter an address to retrieve, the next sequential page is read, when the Read Cache function is issued. After the operation is begun R/B# is set to high (ready) and the host may begin to read the data from the previous Read or Read Cache function. Issuing an additional Read Cache function copies the data most recently read from the array into the cache register. When no more pages are to be read, the final page is copied into the cache register by issuing the 3FH command.

The host may begin to read data from the cache register when R/B# is set to high (ready). When the 31H and 3FH commands are issued, R/B# shall be cleared to low (busy) until the page has finished being copied from the Flash array.

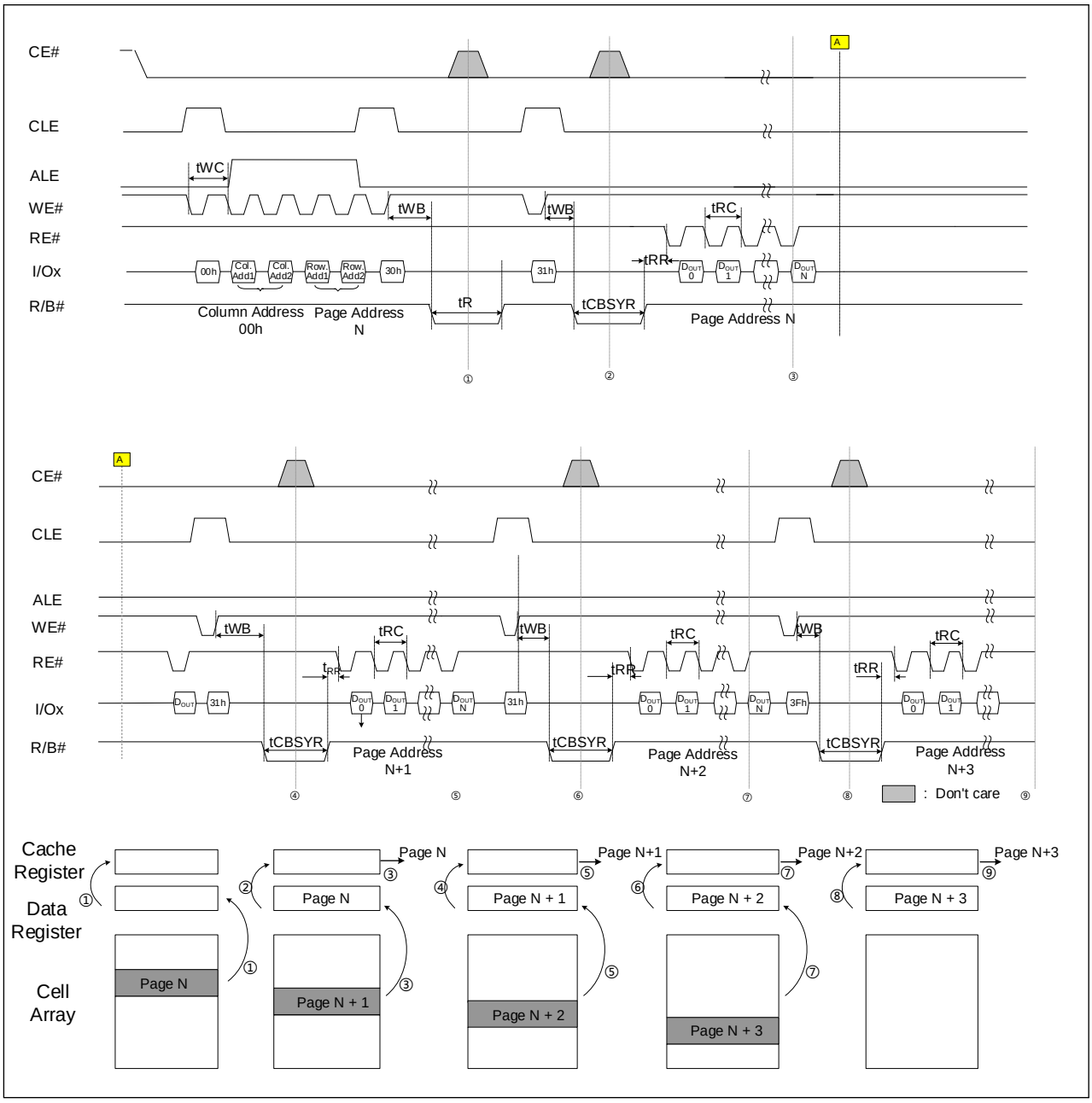


Figure 8-3: Cache Read Operation figures

Note:

ColAdd1- ColAdd2: Column address of the page to retrieve. C1 is the least significant byte.

RowAdd1- RowAdd2: Row address of the page to retrieve. R1 is the least significant byte.

Dout0-DoutN: Data bytes read from page requested by the original Read or the previous cache operation.

8.1.4 Cache Read Random (00H-31H)

The Cache Read Random operation allows the random page to be read-out with cache operation not just for consecutive page only

After issuing the 00h command, the column and row address should be given for the start page selection, and followed by the 30h command for address confirmation. The column address is ignored in the cache read random operation. And then, the Cache Read Random operation starts after a latency time tR and following a 00h command with the selected page address and following a 31h command, the data can be read-out after the latency time of tCBSYR. After the previous selected page data out, a new selected page address can be given by writing the 00h-31h command set again. The Cache Read Random command is also valid for the consecutive page cross block.

The Random Data Output (05h-E0h) command can be used to change the column address of the data being output from the cache register. When no more pages are to be read, the final page is copied into the cache register by issuing the 3FH command in one block.

The host may begin to read data from the cache register when R/B# is set to high (ready). When the 31H and 3FH commands are issued, R/B# shall be cleared to low (busy) until the page has finished being copied from the Flash array.

Status Register can be checked after the Read Status command (70h) is issued. IO6 behaves the same as R/B# pin, IO5 indicates the internal chip operation. “0” means the chip is in internal operation and “1” means the chip is idle. Command 00h should be given to return to the cache read operation.

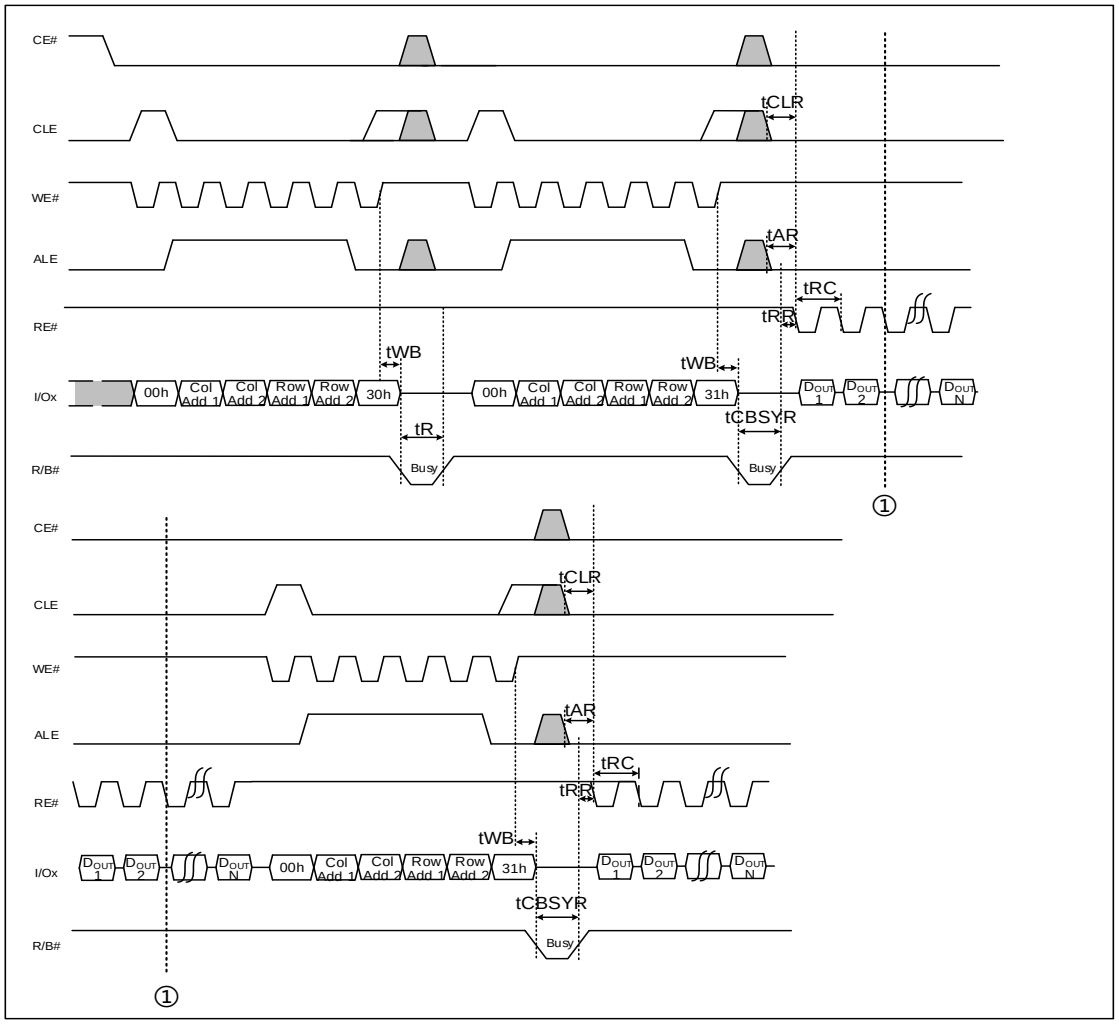


Figure 8-4: Cache Read Random Figure

8.1.5 Read for copy back (00H-35H)

The Copy-Back Read is configured to efficiently rewrite data stored in a page without data reloading when no error within the page is found. The data is read out only at cache register for copy-back program.

Though it is not required, it is recommended that the host read the data out of the device to verify the data prior to issuing the Copy-Back Program (85h-10h) command to prevent the propagation of data errors.

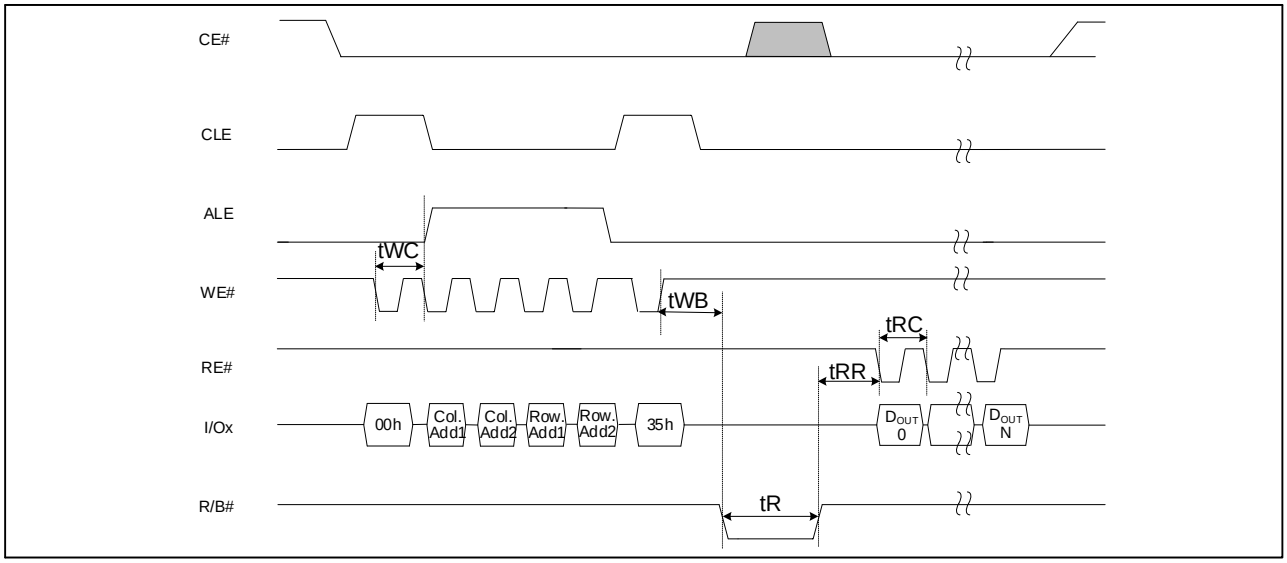


Figure 8-5: Copy-Back read sequential figures

8.2 Page Program Operation

8.2.1 Common Page Program (80H-10H)

The device is programmed basically on a page basis, but it does allow multiple partial pages programming of consecutive bytes up to whole page program cycle. The number of consecutive partial page programming operation within the same page without an intervening erase operation must not exceed NOP.

The page address for programming must be done in sequential order in a block.

A page program cycle consists of a serial data loading period in which up to whole page data may be loaded into the cache register, followed by a non-volatile programming period where the loaded data is programmed into the appropriate cell.

The serial data loading period begins by inputting the Serial Data Input command (80h), followed by the four cycle address inputs and then serial data loading. The bytes other than those to be programmed do not need to be loaded.

The Page Program Confirm command (10h) initiates the programming process. Writing 10h alone without previously entering the serial data will not initiate the programming process. The internal write state controller automatically executes the algorithms and timings necessary for program and verify, thereby freeing the system controller for other tasks. Once the program process starts, the Read Status command may be issued to read the status register.

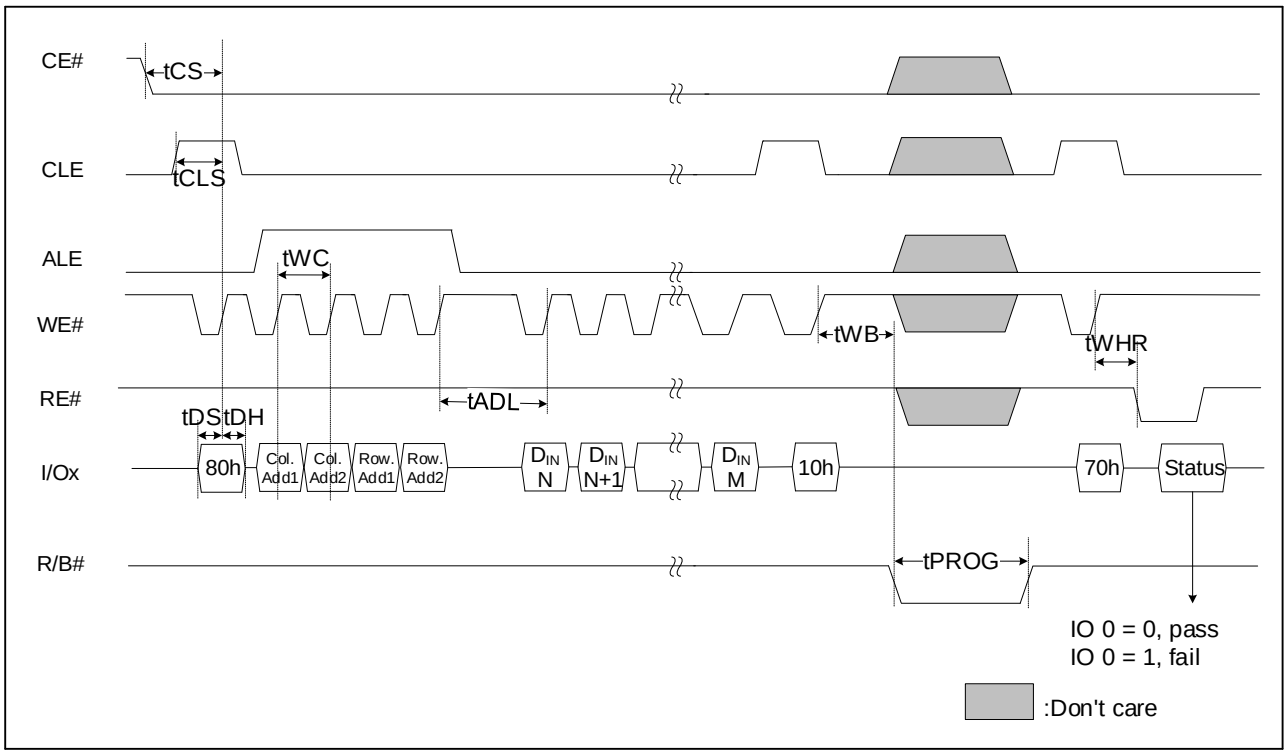


Figure 8-6: Common Page Program figures

8.2.2 Page Program Operation with Random Data Input (85H)

The device supports random data input in a page. The column address of next data, which will be entered, may be changed to the address which follows random data input command (85H). Random data input may be operated multiple times regardless of how many times it is done in a page.

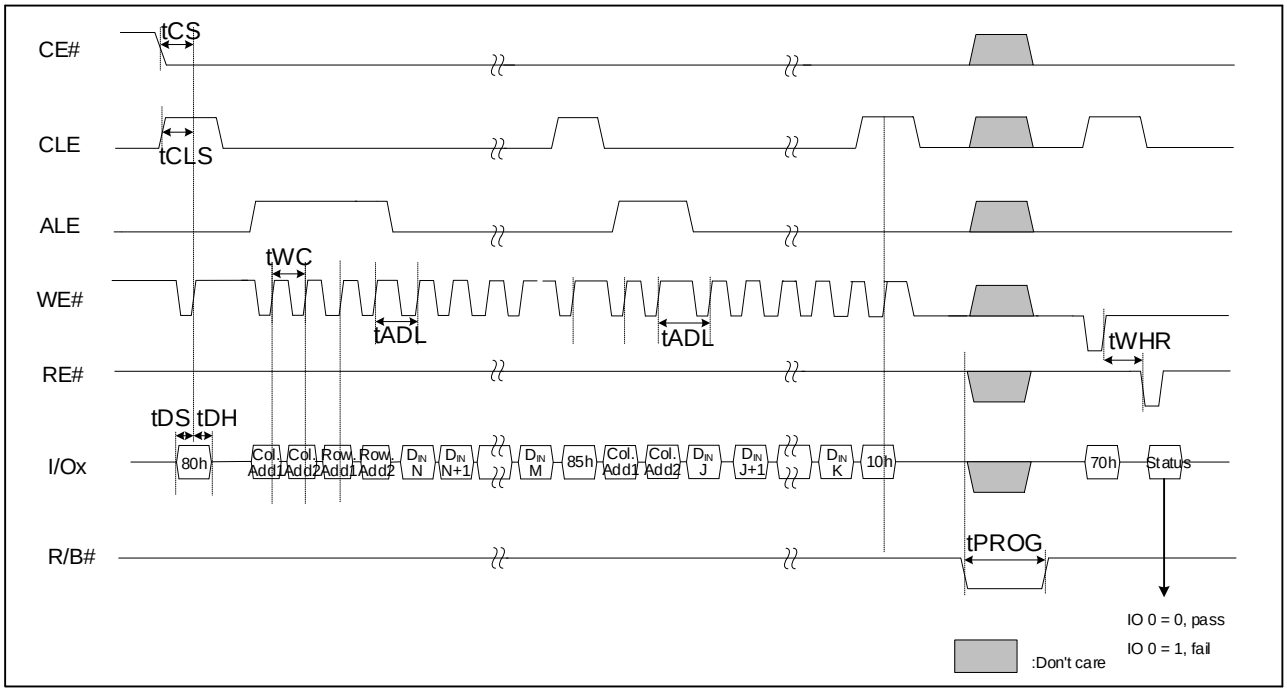


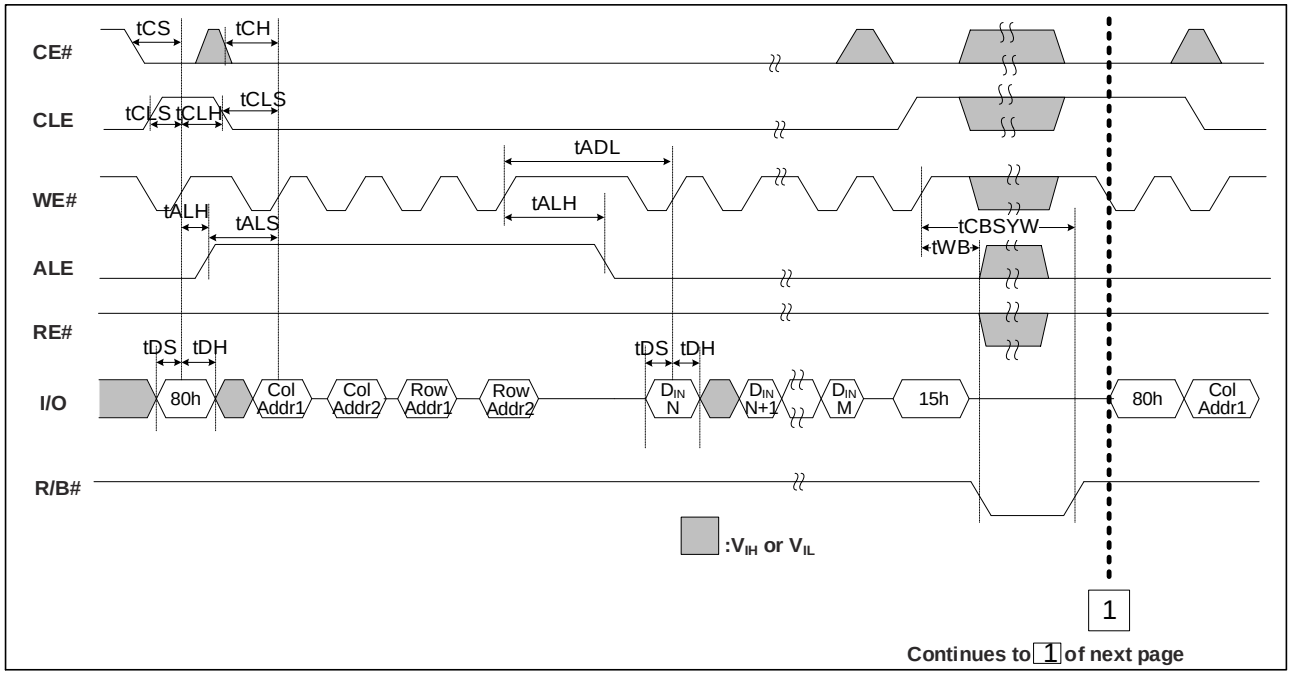
Figure 8-7: Page Program Operation with Random Data Input figures

8.2.3 Cache Program Operation (80H-15H)

Cache Program is an extension of Page Program, which is executed with one cache register and one data register, and is available only within a block. Since the device has one page of cache register, serial data input may be executed while data stored in data register are programmed into memory cell.

After writing the first set of data up to one page into the selected cache register, Cache Program command (15H) instead of actual Page Program (10H) is inputted to make cache register free and to start internal program operation. To transfer data from cache register to data register, the device remains in Busy state for a short period of time (tCBSYW) and has its cache register ready for the next data-input while the internal programming gets started with the data loaded into data register. Read Status command (70H) may be issued to find out when cache register become ready by polling the Cache-Busy status bit (I/O6). Pass/fail status of only the previous page is available upon the return to Ready state. When the next set of data is loaded with the Cache Program command, tCBSYW is affected by the progress of pending internal programming. The programming of the cache register is initiated only when the pending program cycle is finished and the data register are available for the transfer of data from cache register. The status bit (I/O5) for internal Ready/Busy may be polled to identify the completion of internal programming. If the system monitors the progress of programming only with R/B#, the last page of the target programming sequence must be programmed with actual Page Program command

(10H). If, after tCBSYW, the host wants to wait for the PROGRAM CACHE operation to complete, without issuing the PROGRAM PAGE (80h-10h) command, the host should monitor ARDY until it is 1. The host should then check the status of the FAIL and FAILC bits.



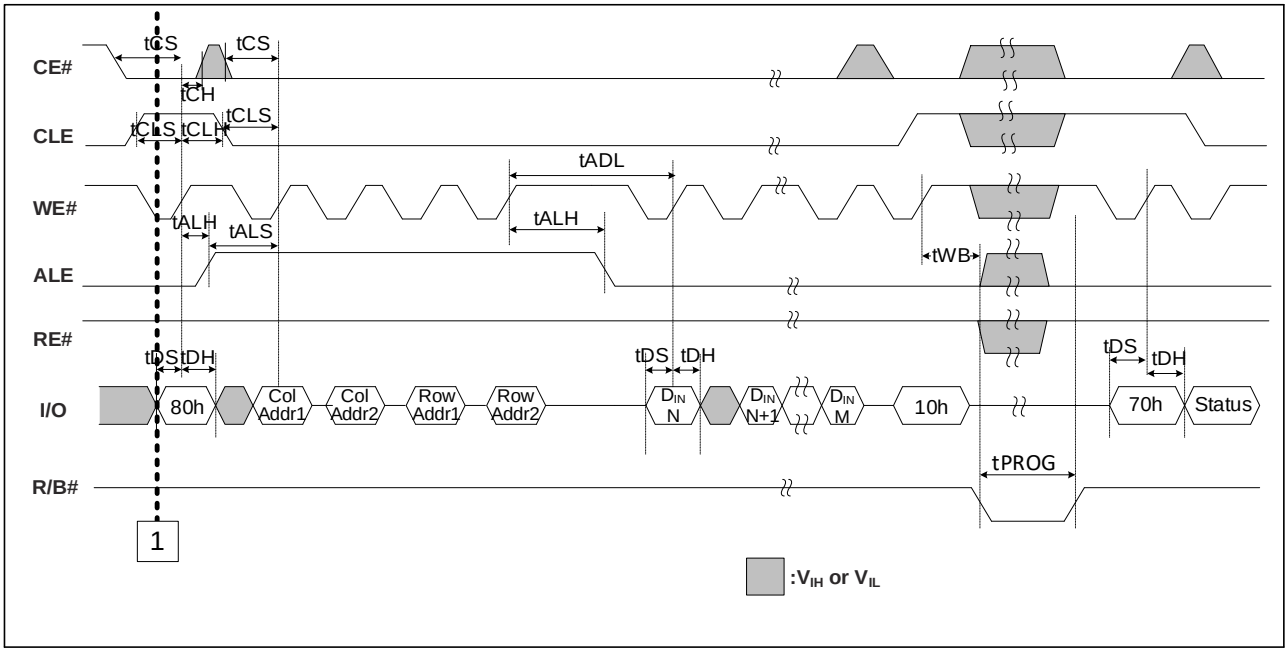


Figure 8-8: Cache Program Operation figures

8.2.4 Copy-Back Program with Random Data Input (85H-10H)

The copy-back program is configured to quickly and efficiently rewrite data stored in one page without utilizing an external memory. Since the time-consuming cycles of serial access and re-loading cycles are removed, the system performance is improved.

The benefit is especially obvious when a portion of a block is updated and the rest of the block is also needed to be copied to the newly assigned free block.

The operation for performing a copy-back program is a sequential execution of page-read without serial access and copying-program with the address of destination page. A read operation with “35h”command and the address of the source page moves the whole page bytes data into the internal cache register. As soon as the device returns to Ready state, optional data read-out is allowed by toggling RE#, or Copy Back command (85H) with the address cycles of destination page may be written. The Program Confirm command (10H) is required to actually begin the programming operation. Data input cycle for modifying a portion or multiple distant portions of the source page is allowed. When there is a program-failure at Copy-Back operation, error is reported by pass/fail status. But, if Copy-Back operations are accumulated over time, bit error due to charge loss is not checked by external error detection/correction scheme.

Please note that Random Data Input (with/without data) is entered before Program Confirm command (10H) after Random Data output.

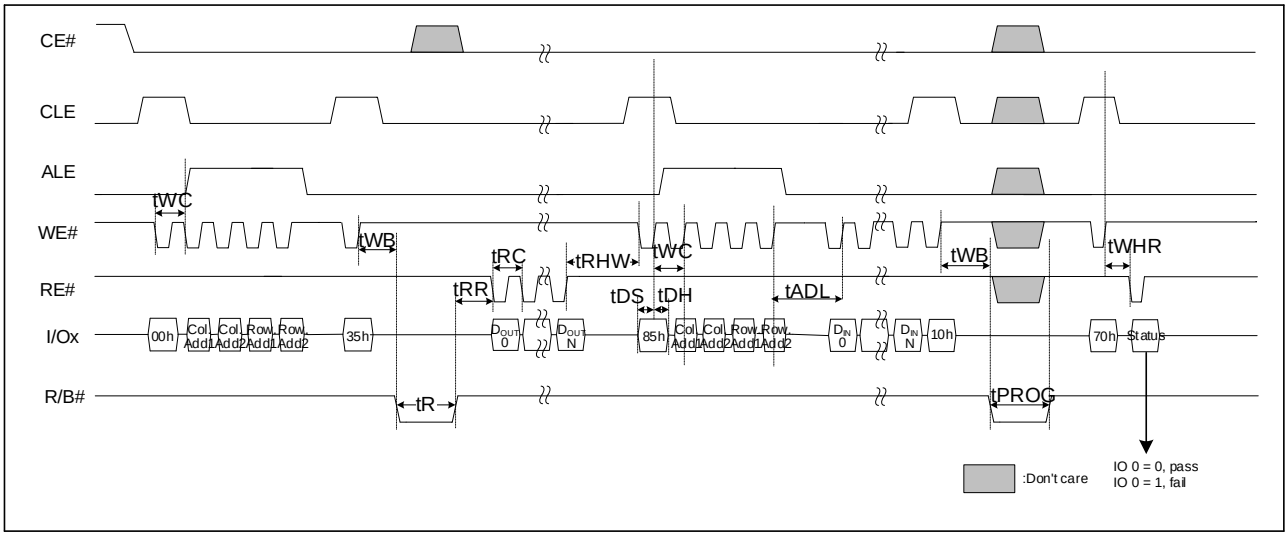


Figure 8-9: Copy-Back Program with Random Data Input figures

Note: the data followed with 85h command is optional

8.3 Block Erase Operation

8.3.1 Common Block Erase Operation (60H-D0H)

The Erase operation is done on a block basis. Block address loading is accomplished in three cycles initiated by an Erase Setup command (60H). Row Address is valid while Column Addresses ignored. The Erase Confirm command (D0H) following the block address loading initiates the internal erasing process. At the rising edge of WE# after the erase confirm command input, the NAND device handles erase and erase verify. Once the erase process starts, the Read Status Register command may be entered to read the status register. The system controller can detect the completion of an erase by monitoring the R/B# output, or the Status bit (I/O6) of the Status Register. Only the Read Status command and Reset command are valid while erasing is in progress. When the erase operation is completed, the Write Status Bit (I/O 0) may be checked.

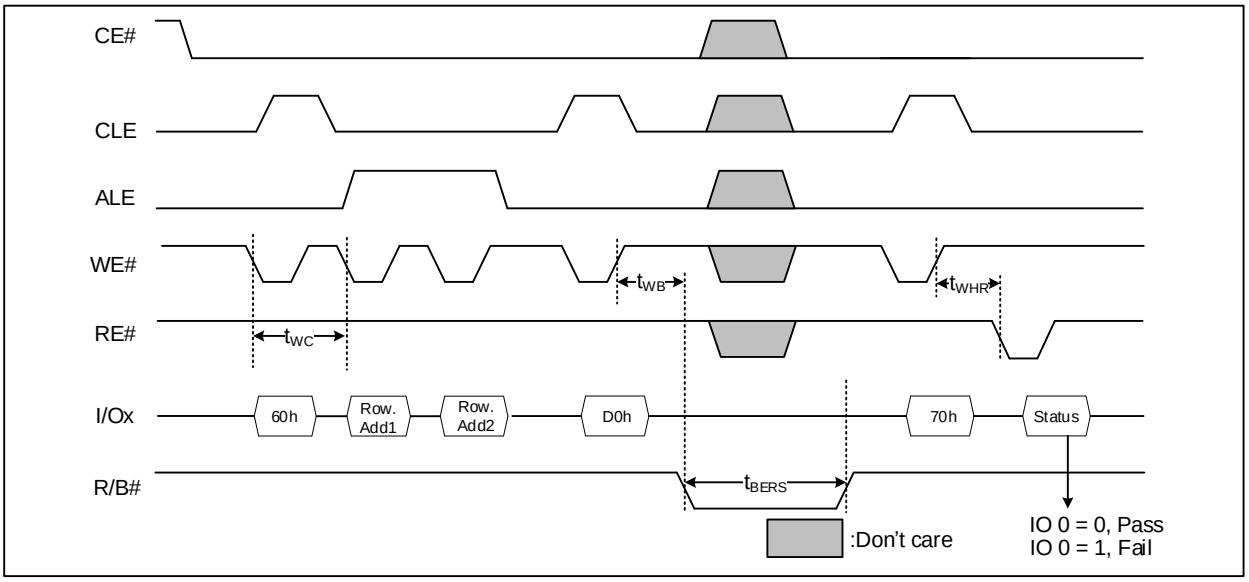


Figure 8-10: Common Block Erase Operation figures

8.4 Reset (FFH)

8.4.1 Reset (FFH)

The device offers a reset feature, executed by writing FFH to the command register. When the device is in busy state during random read, program or erase mode, the reset operation will abort these operations. The contents of memory cells being altered are no longer valid, as the data will be partially programmed or erased. The command register is cleared to wait for the next command, and the Status Register is cleared to value E0h when R/B# is high and WP# is high. If the device is already in reset state a new reset command will be accepted by the command register. The R/B# pin will change to low for tRST after the Reset command is written.

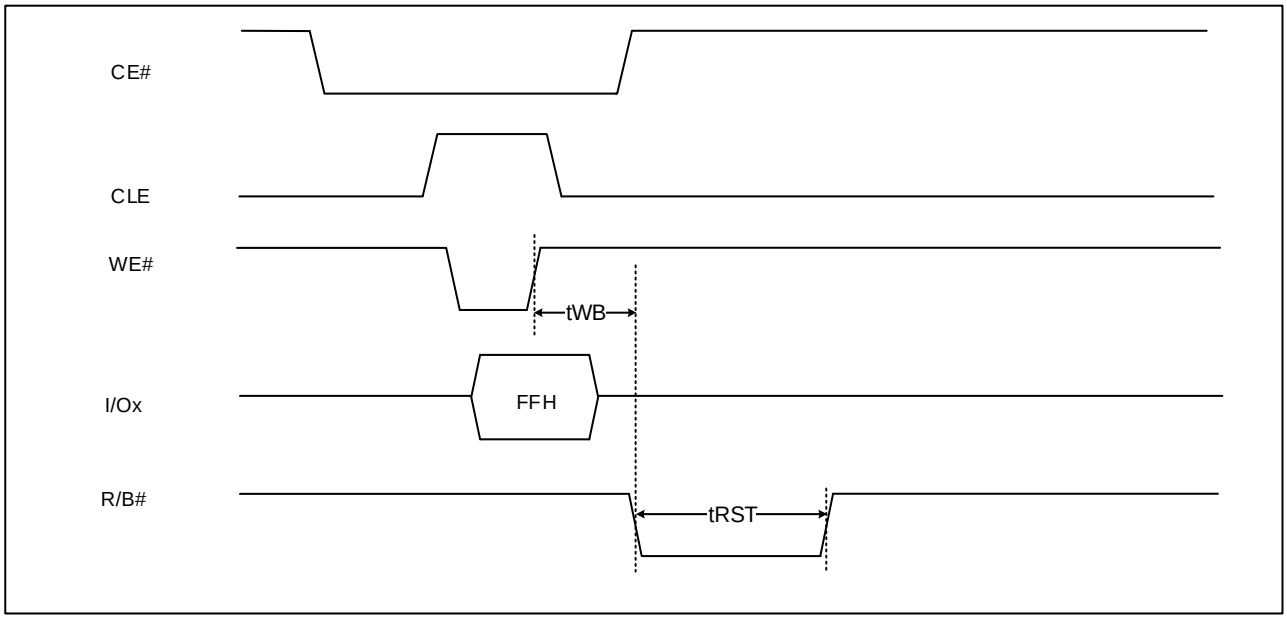


Figure 8-11: Reset (FFH) figures

8.5 Read Device Information

8.5.1 Read ID and ONFI Signature (90H)

The device contains a product identification mode, initiated by writing 90H to the command register, followed by an address input of 00H. Five read cycles sequentially output the manufacturer code, and the device code and other information, respectively. The command register remains in Read ID mode until further commands are issued to.

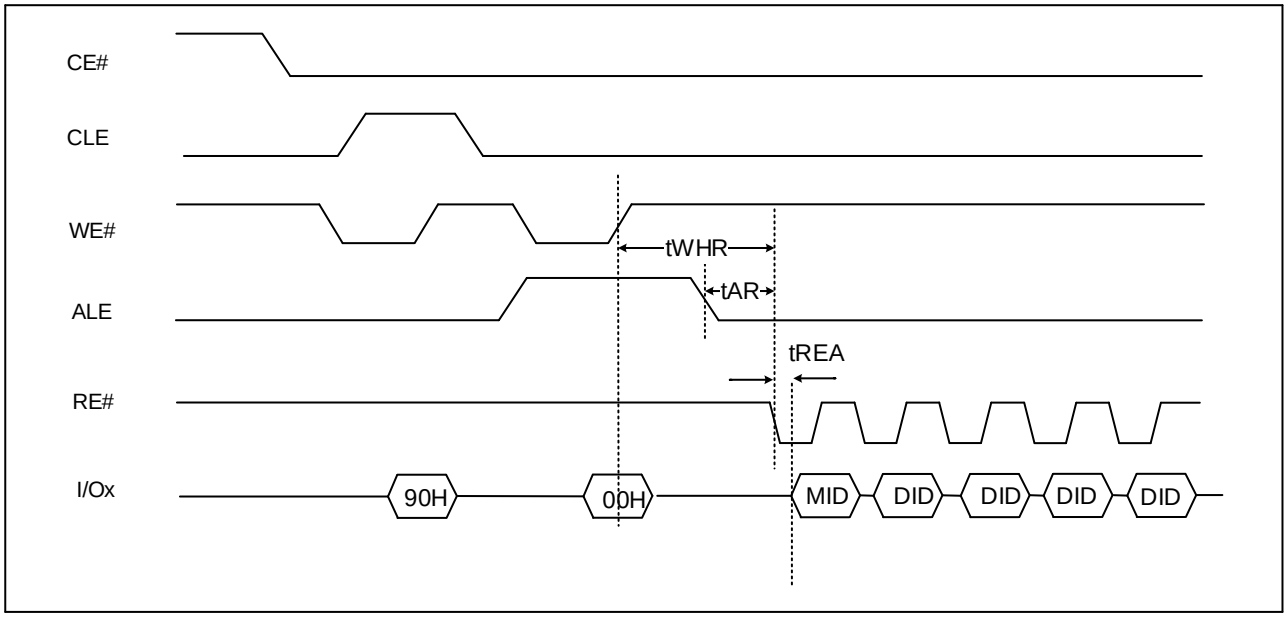


Figure 8-12: Read ID figures

ID Definition Table

Byte	Description
1st Byte	Manufacturer Code (MID)
2nd Byte	Device Code (DID)
3rd Byte	Internal Chip Number, Cell Type, Number of Simultaneously Programmed Pages, Interleaved Program, Write Cache
4th Byte	Page size, Block size, Spare size, Organization
5th Byte	ECC & Plane

Read ID Data Table

Part Number	VCC	Bus Width	MID(1st)	DID(2nd)	3rd	4th	5th
GD9FU1G8F2D	3.3v	x8	C8	F1	80	95	43
GD9FS1G8F2D	1.8v	x8	C8	A1	80	15	43

3rd Byte of Device Identifier Description

3rd Cycle	Description	IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0
Internal Chip Number	1							0	0
	2							0	1
	4							1	0
	8							1	1
Cell Type	2 Level Cell					0	0		
	4 Level Cell					0	1		
	8 Level Cell					1	0		
	16 Level Cell					1	1		
Number of Simultaneously Programmed Pages	1			0	0				
	2			0	1				
	4			1	0				
	8			1	1				
Interleaved Program Between Multiple Die	Not Supported		0						
	Supported		1						
Write Cache (Cache Programming)	Not Supported	0							
	Supported	1							

4th Byte of Device Identifier Description

4th Cycle	Description	IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0
Page Size (without Spare Area)	1KB							0	0
	2KB							0	1
	4KB							1	0
	8KB							1	1
Size of spare area (byte per 512-byte)	32						1		
Serial Access Time	20ns	0				0			
	12ns	1				0			
Block Size (Without Spare Area)	64KB			0	0				
	128KB			0	1				
	256KB			1	0				
	512KB			1	1				
Organization	x8		0						
	x16		1						

5th Byte of ECC & Plane

5th Cycle	Description	IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0
ECC Level	1							0	0
	2							0	1
	4							1	0
	8							1	1
Plane Number per CE#	1					0	0		
	2					0	1		
	4					1	0		
	8					1	1		
Reserved			1	0	0				
Internal ECC	ECC disabled	0							
	ECC enabled	1							

To retrieve the ONFI signature, the command 90H together with an address of 20H shall be entered. The ONFI signature is the ASCII encoding of 'ONFI' where 'O' = 4FH, 'N' = 4EH, 'F' = 46H, and 'I' = 49H. Reading beyond four bytes yields indeterminate values.

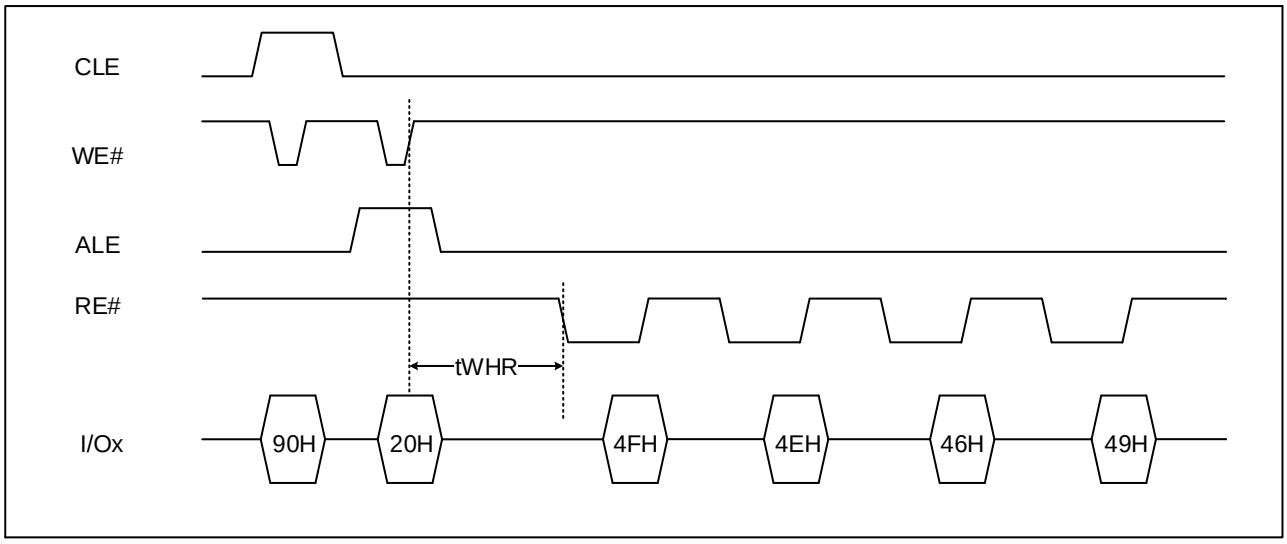


Figure 8-13: Read ONFI Signature figures

8.5.2 Read Unique ID (EDH)

The Read Unique ID function is used to retrieve the 16 byte unique ID (UID) for the device. The unique ID when combined with the device manufacturer shall be unique.

The UID data may be stored within the Flash array. To allow the host to determine if the UID is without bit errors, the UID is returned with its complement. If the XOR of the UID and its bit-wise complement is all ones, then the UID is valid. To accommodate robust retrieval of the UID in the case of bit errors, sixteen copies of the UID and the corresponding complement shall be stored by the target. For example, reading bytes 32-63 returns to the host another copy of the UID and its complement.

To change the data output location, it is recommended to use the Random Data Out command set (05H-E0H).The Status Read command (70H) can be used to check the completion. To continue the read operation, a following read command (00h) to re-enable the data out is necessary.

Bytes	Value
0-15	UID
16-31	UID complement (bit-wise)

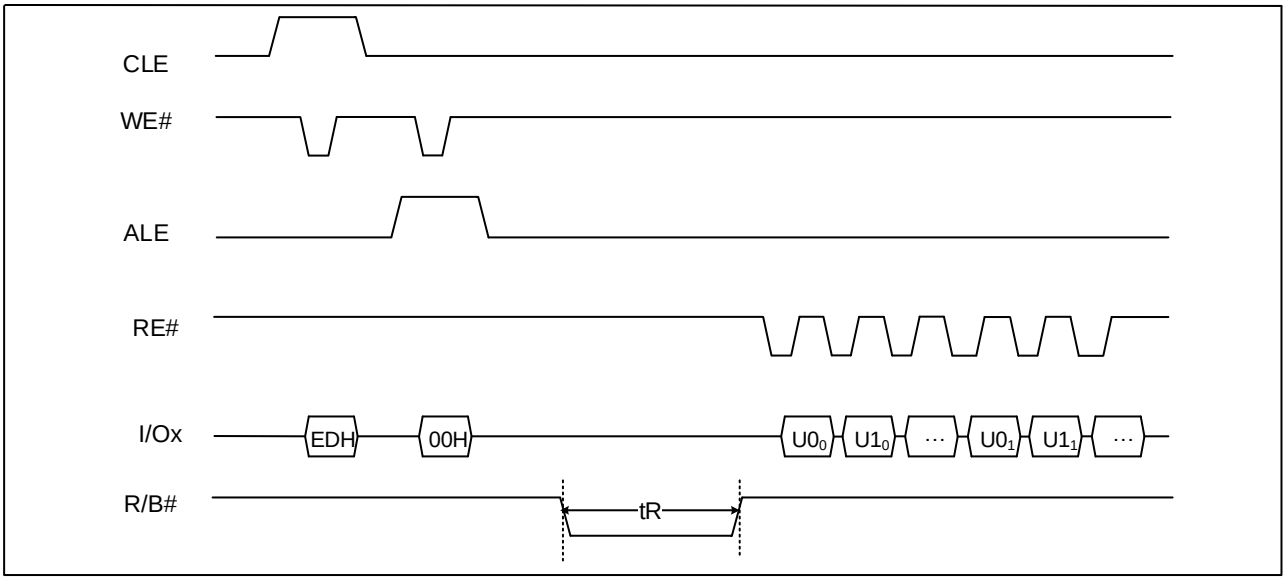


Figure 8-14: Read Unique ID figures

8.5.3 Read Parameter Page (ECH)

The Read Parameter Page function retrieves the data structure that describes the chip's organization, features, timings and other behavioral parameters. This data structure enables the host processor to automatically recognize the NAND Flash configuration of a device. A minimum of three copies of the parameter page are stored in the device. The Random Data Read command (05H-E0H) can be used to change the location of data output. The Read Status command (70H) may be used to check the status of read parameter page during execution. After completion of the Read Status command, 00H is issued by the host on the command line to continue with the data output flow for the Read Parameter Page command.

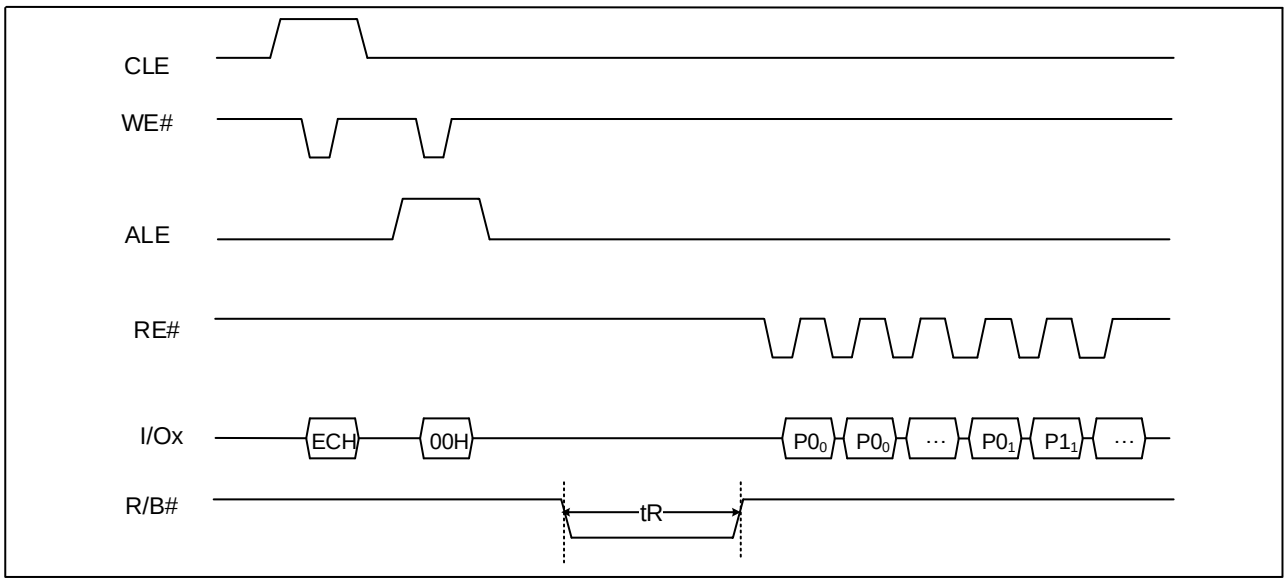


Figure 8-15: Read Parameter Page figures

Byte	O/M	Description	1Gb
0-3	M	Parameter page signature Byte 0: 4FH, “O” Byte 1: 4EH, “N” Byte 2: 46H, “F” Byte 3: 49H, “I”	4FH 4EH 46H 49H
4-5	M	Revision number 2-15 Reserved (0) 1 1 = supports ONFI version 1.0 0 Reserved (0)	02H 00H
6-7	M	Features supported 5-15 Reserved (0) 4 1 = supports odd to even page Copy back 3 1 = supports interleaved operations 2 1 = supports non-sequential page programming 1 1 = supports multiple LUN operations 0 1 = supports 16-bit data bus width	10H(X8) 00H
8-9	M	Optional commands supported 6-15 Reserved (0) 5 1 = supports Read Unique ID 4 1 = supports Copy-back 3 1 = supports Read Status Enhanced 2 1 = supports Get Features and Set Features 1 1 = supports Page Cache Read command 0 1 = supports Page Cache Program command	37H 00H
10-31		Reserved (0)	00H … 00H
		Manufacturer Information block	
32-43	M	Device manufacturer (12 ASCII characters)“GIGADEVICE”	47H 49H 47H 41H 44H 45H 56H 49H 43H 45H 20H 20H

<table>
<tr><td>44-63</td><td>M</td><td>Device model (20 ASCII characters)<table><tr><th>Device Model</th><th>ORGANIZATION</th><th>VCC RANGE</th></tr><tr><td>GD9FU1G8F2D</td><td>128M x 8bit</td><td>2.7v ~ 3.6v</td></tr><tr><td>GD9FS1G8F2D</td><td>128M x 8bit</td><td>1.7v ~ 1.95v</td></tr></table></td><td>47H
44H
39H
46H
53H/55H
(1.8V/3.3V)
31H
47H
38H(X8)
46H
32H
44H
20H
20H
20H
20H
20H
20H
20H
20H
20H
20H</td></tr>
<tr><td>64</td><td>M</td><td>JEDEC manufacturer ID“C8”</td><td>C8H</td></tr>
<tr><td>65-66</td><td>O</td><td>Date code</td><td>00H
00H</td></tr>
<tr><td>67-79</td><td></td><td>Reserved</td><td>00H
00H
00H</td></tr>
<tr><td></td><td></td><td>Memory organization block</td><td></td></tr>
<tr><td>80-83</td><td>M</td><td>Number of data bytes per page</td><td>00H
08H
00H
00H</td></tr>
<tr><td>84-85</td><td>M</td><td>Number of spare bytes per page</td><td>80H
00H</td></tr>
<tr><td>86-89</td><td>M</td><td>Number of data bytes per partial page</td><td>00H
02H
00H
00H</td></tr>
<tr><td>90-91</td><td>M</td><td>Number of spare bytes per partial page</td><td>20H
00H</td></tr>
<tr><td>92-95</td><td>M</td><td>Number of pages per block</td><td>40H
00H
00H
00H</td></tr>
</table>

96-99	M	Number of blocks per logical unit (LUN)	00H 04H 00H 00H
100	M	Number of logical units (LUNs)	01H
101	M	Number of address cycles 4-7 Column address cycles 0-3 Row address cycles	22H
102	M	Number of bits per cell	01H
103-104	M	Bad blocks maximum per LUN	14H 00H
105-106	M	Block endurance	05H 04H
107	M	Guaranteed valid blocks at beginning of target	01H
108-109	M	Block endurance for guaranteed valid blocks	00H 00H
110	M	Number of programs per page	04H
111	M	Partial programming attributes 5-7 Reserved 4 1 = partial page layout is partial page data followed by partial page spare 1-3 Reserved 0 1 = partial page programming has constraints	00H
112	M	Number of bits ECC correct ability	08H
113	M	Number of interleaved address bits 4-7 Reserved (0) 0-3 Number of interleaved address bits	00H
114	O	Interleaved operation attributes 4-7 Reserved (0) 3 1 = Address restrictions for program cache 2 1 = program cache supported 1 1 = no block address restrictions 0 1= Overlapped / concurrent interleaving support	00H
115-127		Reserved	00H … 00H
		Electrical parameters block	
128	M	I/O capacitance	06H

129-130	M	Timing mode support 6-15 Reserved (0) 5 1 = supports timing mode 5 4 1 = supports timing mode 4 3 1 = supports timing mode 3 2 1 = supports timing mode 2 1 1 = supports timing mode 1 0 1 = supports timing mode 0, shall be 1	3FH(3.3V)/ 3FH(1.8V) 00H
131-132	O	Program cache timing mode support 6-15 Reserved (0) 5 1 = supports timing mode 5 4 1 = supports timing mode 4 3 1 = supports timing mode 3 2 1 = supports timing mode 2 1 1 = supports timing mode 1 0 1 = supports timing mode 0,	3FH(3.3V)/ 3FH(1.8V) 00H
133-134	M	tPROG Maximum page program time (us)	58H 02H
135-136	M	tBERS Maximum block erase time (us)	10H 27H
137-138	M	tR Maximum page read time (us)	19H 00H
139-140	M	tCCS Minimum Change Column setup time (ns) (N/A)	50H 00H
141-163		Reserved	00H
		Vendor block	
164-165	M	Vendor specific Revision number	00H
166-253		Vendor specific	00H
254-255	M	Integrity CRC	
		Redundant parameter pages	
256-511	M	Value of bytes 0-255	
512-767	M	Value of bytes 0-255	
768+	O	Additional redundant parameter pages	

Notes:

1. “O” Stands for Optional, “M” for Mandatory
2. The Integrity CRC (Cycling Redundancy Check) field is used to verify that the contents of the parameters page were transferred correctly to the host. Please refer to ONFI 1.0 specifications for details.

   The CRC shall be calculated using the following 16-bit generator polynomial: $G(X) = X16 + X15 + X2 + 1$, This polynomial in hex may be represented as 8005h.

3. The CRC value shall be initialized with a value of 4F4Eh before the calculation begins. There is no XOR applied to the final CRC value after it is calculated. There is no reversal of the data bytes or the CRC calculated value.

Parameter page CRC value table

Device Model	ORGANIZATION	VCC RANGE	CRC value B254/B255
GD9FS1G8F2D	128M x 8bit	1.7v ~ 1.95v	64H/44H
GD9FU1G8F2D	128M x 8bit	2.7v ~ 3.6v	89H/60H

8.6 Read Status (70H)

The device contains a Status Register which may be read to find out whether an operation is completed and whether the program or erase operation is completed successfully. After writing 70H command to the command register, a read cycle outputs the content of the Status Register to the I/O pins on the falling edge of CE# or RE#, whichever occurs last. This allows the system to poll the progress of each device in multiple memory connections even when R/B# pins are common-wired. RE# or CE# does not need to be toggled for updated status. The command register remains in Status Read mode until further commands are issued to it. Therefore, if the status register is read during a random read cycle, the read command (00h) should be given before starting read cycles.

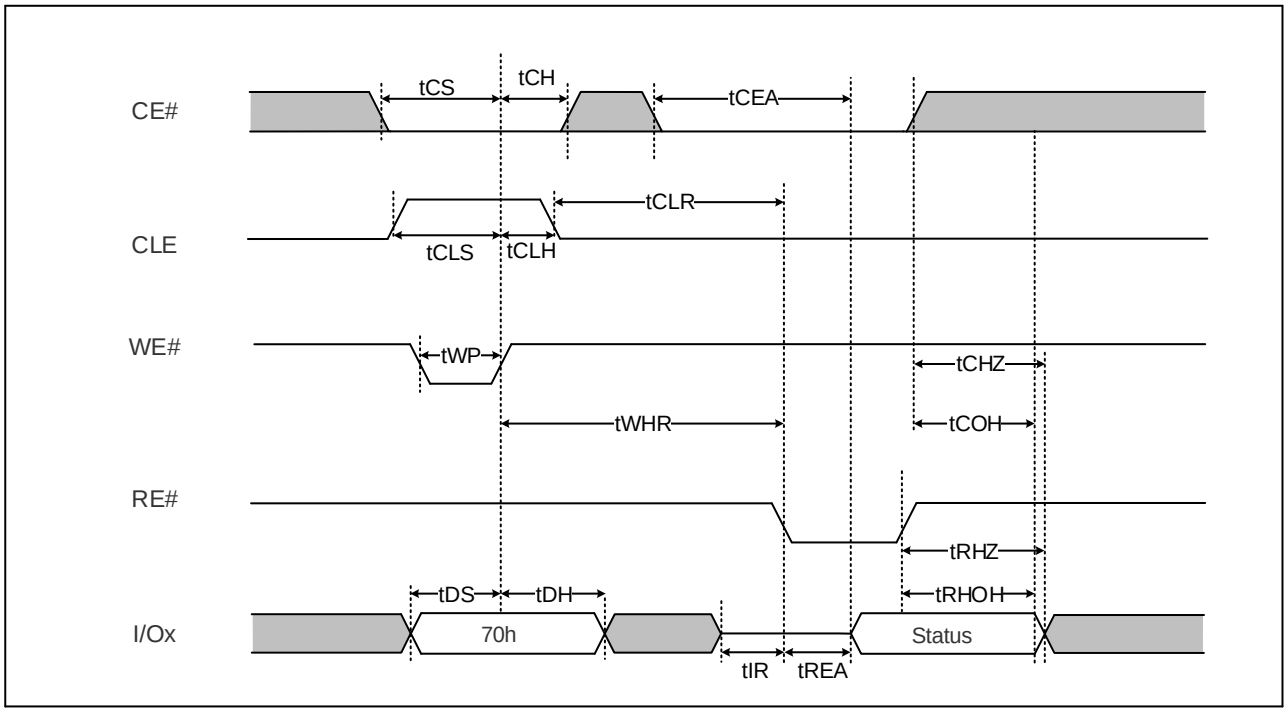


Figure 8-16: Read Status figures

I/O No.	Page Program	Block Erase	Cache Program	Read	Cache Read	Definition
I/O0	Pass/Fail	Pass/Fail	Pass/Fail(N)	-	-	FAIL N Page Pass : 0 Fail : 1
I/O1	-	-	Pass/Fail(N-1)	-	-	FAILC N-1 Page Pass : 0 Fail : 1
I/O2	-	-	-	-	-	Don't Care
I/O3	-	-	-	-	-	Don't Care
I/O4	-	-	-	-	-	Don't Care
I/O5	Ready/Busy	Ready/Busy	Ready/Busy	Ready/Busy	Ready/Busy	ARDY Ready/Busy for Array Operation Busy : 0 Ready : 1
I/O6	Ready/Busy	Ready/Busy	Ready/Busy	Ready/Busy	Ready/Busy	RDY Ready/Busy Busy : 0 Ready : 1
I/O7	Protected/ Not Protected	Protected/ Not Protected	Protected/ Not Protected	Protected/ Not Protected	Protected Not Protected	Protected:0 Not Protected:1

Notes:

1. I/O0: This bit is only valid for Program and Erase operations. During Cache Program operations, this bit is only valid when I/O5 is set to 1.
2. I/O1: This bit is only valid for cache program operations. This bit is not valid until after the second 15h command or the 10h command has been transferred in a Cache program sequence.
3. I/O5: If set to one, then there is no array operation in progress. If cleared to zero, then there is a command being processed (I/O6 is cleared to zero) or an array operation in progress.
4. I/O6: When cache operations are in use, then this bit indicates whether another command can be accepted, and I/O5 indicates whether the operation is complete.
5. I/O7: the bit indicates if the block is protected, which include WP# protection and other protection.

8.7 Set Feature (EFH)

Users may set particular features using 'Set Feature' operation. Once a feature is set by users, it shall not be changed until the device is powered off or setting is changed by users. Figure of "Set Feature Sequence" defines the Set Features behavior and timings and follow Table defines features that users can change. These settings are not retained across the power off. Note that FFh command is not allowed during SET FEATURE sequence.

The NAND device may remain the current feature set until next power cycle since the feature set data is volatile. However, the reset command (FFh) cannot reset the current feature setting unless otherwise specified in the features table

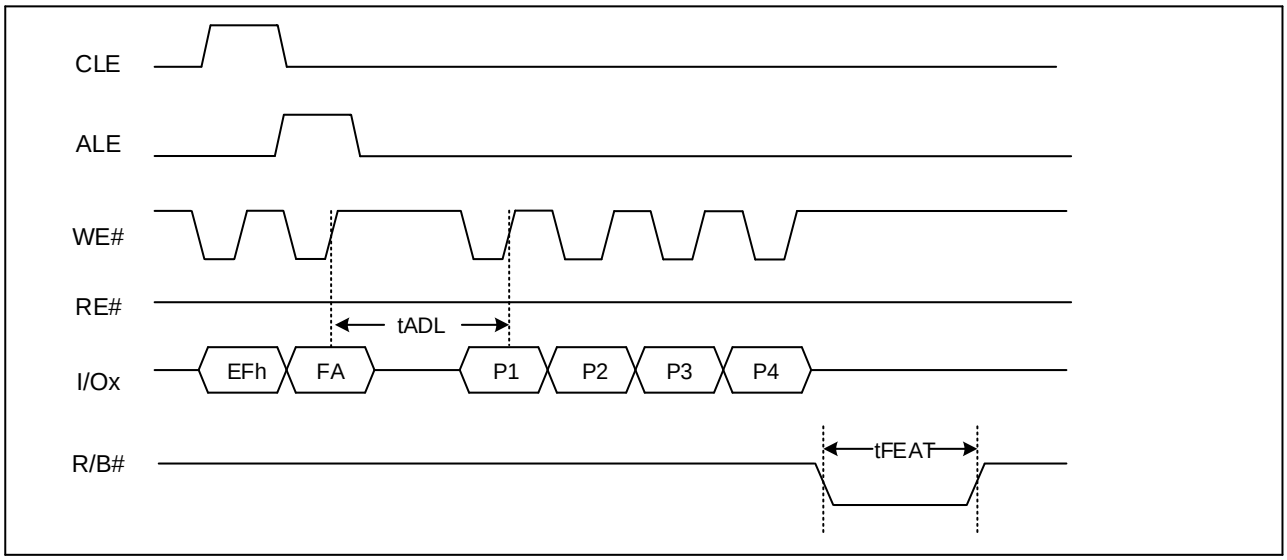


Figure 8-17: Set Feature (EFH) sequential figures

Note: FA, feature address

Table Feature address define

Command cycle	Feature address	Description
EFH	80h	Output Driver strength setting
	Other	Reserved

Table Feature address 80h: Output Driver strength setting

Feature parameter	Option	IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0	value	Note
P1	Overdrive2	0	0	0	0	0	0	0	0	00h	1
	Overdrive1	0	0	0	0	0	0	0	1	01h	
	Normal	0	0	0	0	0	0	1	0	02h	
	Under drive	0	0	0	0	0	0	1	1	03h	
P2	Reserved	0	0	0	0	0	0	0	0	00h	
P3	Reserved	0	0	0	0	0	0	0	0	00h	
P4	Reserved	0	0	0	0	0	0	0	0	00h	

Note1: Default is 00h

See follow Output Drive Strength Impedance Values table for details. Output Driver Strength Settings

Setting	Driver Strength	VCC
Overdrive 2	2.0x	3.3V/1.8V
Overdrive 1	1.4x	
Normal	1.0x	
Under drive	0.5x	

8.8 Get Feature (EEH)

Users find how the target is set through 'Get Feature' command. The function shall return the current setting information. (Including modifications that may have been previously made with the Set Features function). If a host starts to read the first byte of data (i.e. P1 value), the host shall complete reading all four bytes of data before issuing another command (including Read Status or Read Status Enhanced). Follow figure of "Get Feature Sequence" defines the Get Features behavior and timings.

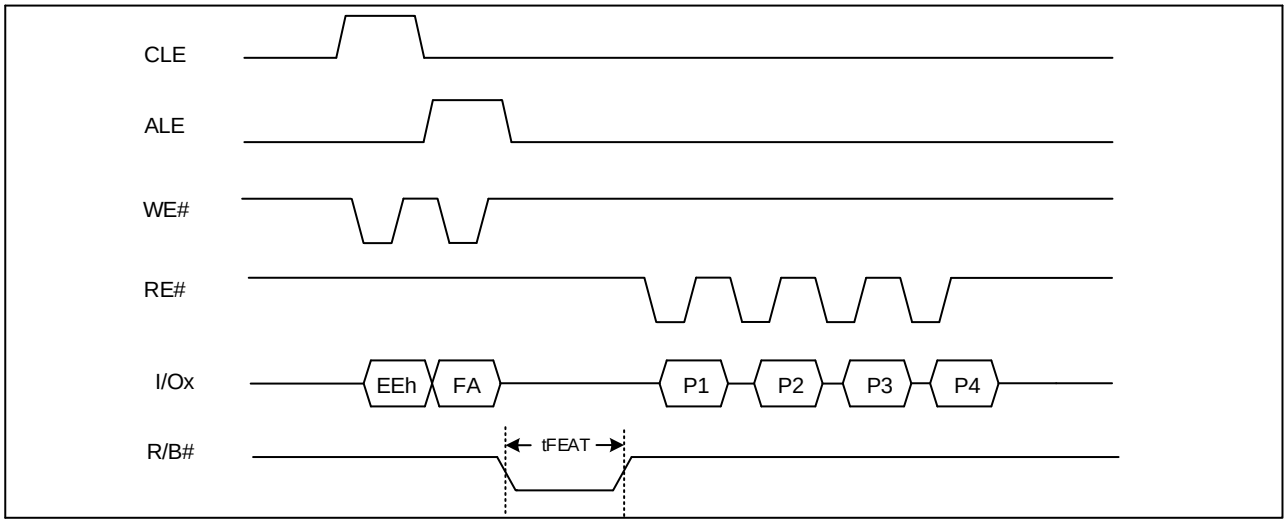


Figure 8-18: Get Feature (EEH) sequential figures

P1~P4 is the returned information with get feature command, which is same as the content of set feature command.

8.9 Global Protection

Global protection provides an additional level of protection against inadvertent PROGRAM and ERASE operations to locked blocks. Once the Global Protection command is enabled, the protect blocks cannot be reset by RESET command, only another power cycle can disable the Global Protection.

Global Protection enter special command sequence of 4Ch-03h-1Dh-42h to the command cycle with five-byte data as follow figure.

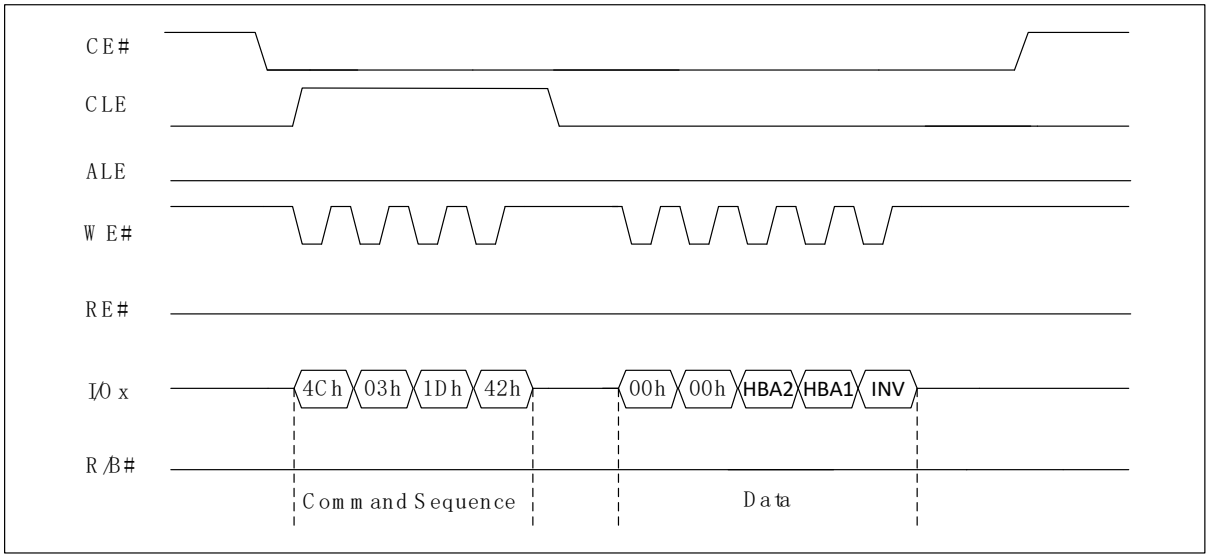


Figure 8-19 Set Global Protection Figure

{00h,00h}	**Block0**
{HBA2,HBA1}	**High block address**
INV = 8'h00	**Block0=<Protection block address <= High block address**
INV = 8'hFF	**High block address<Protection block address <=Last block**

Note:

1. High block address {HBA2,HBA1} definition:
   HBA2 means MSB and HBA1 means LSB of the high block address.
   For example, if high block address is block 1023, then {HBA2, HBA1} = {03H, FFH}.

2. Block global protection status
   1) Send 00h + Block Address (Full four-byte address)
   2) Send reading status register command 70h to check the last operation block protection status.
   IO7=1: the last block is unprotected

IO7=0: the last block is protected

3. Protection status of each block can be read

If program or erase a protected block, R/B# goes LOW for tPBSY, the PROGRAM or ERASE operation does not complete. And then Read status command (70h) reports bit 7 as 0, indicating that the block is protected

4. Protection Valid Cycle

The protected block is valid during a power cycle, and cannot be changed by FW in current power cycle.

And user need re-set the protection block in another new power cycle.

8.10 Ready/Busy# (R/B#)

The device has a Ready/Busy output that provides method of indicating the completion of a page program, erase, copy-back and random read completion. The R/B# pin is normally high and goes to low when the device is busy (after a reset, read, program, and erase operation). It returns to high when the internal controller has finished the operation. The pin is an open-drain driver thereby allowing two or more R/B# outputs to be Or-tied. Because pull-up resistor value is related to tr (R/B#), an appropriate value can be obtained with the following reference below chart. Its value can be determined by the following guidance.

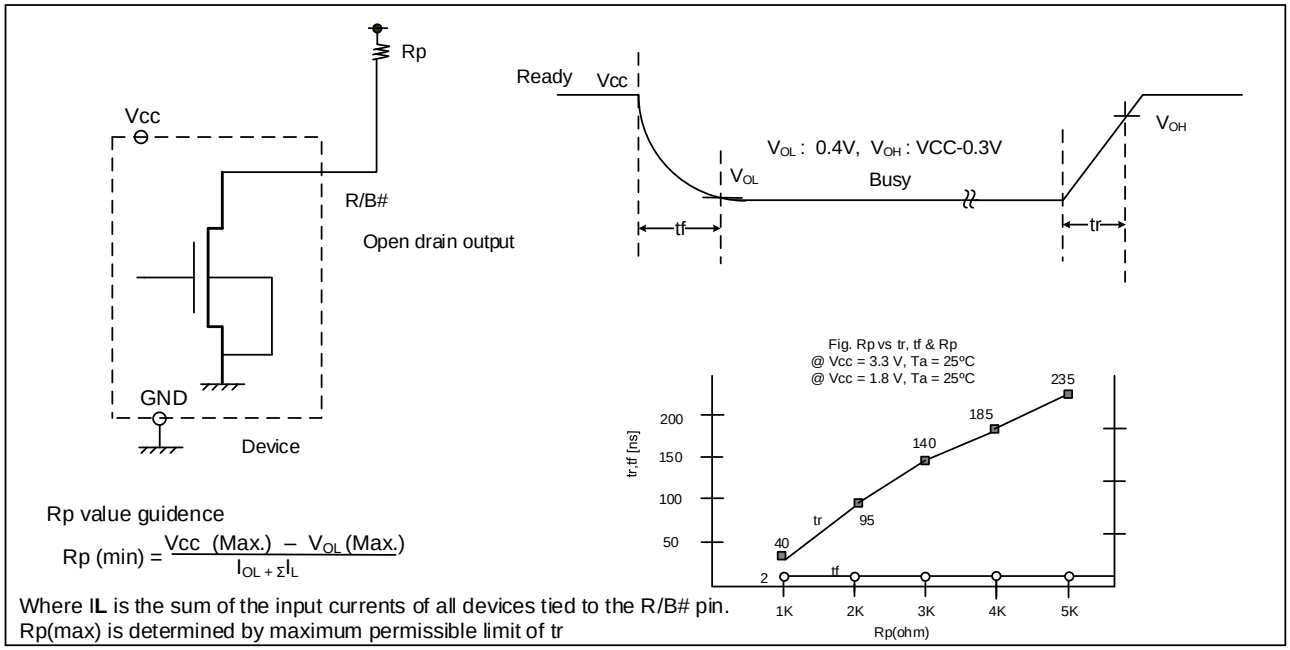


Figure 8- 20: Ready/Busy figures

8.11 Data Protection & Power on/off Sequence

The device is designed to offer protection from any involuntary program/erase during power-transitions. WP# pin provides hardware protection and is recommended to be kept at V_{IL} during power-up and power-down.

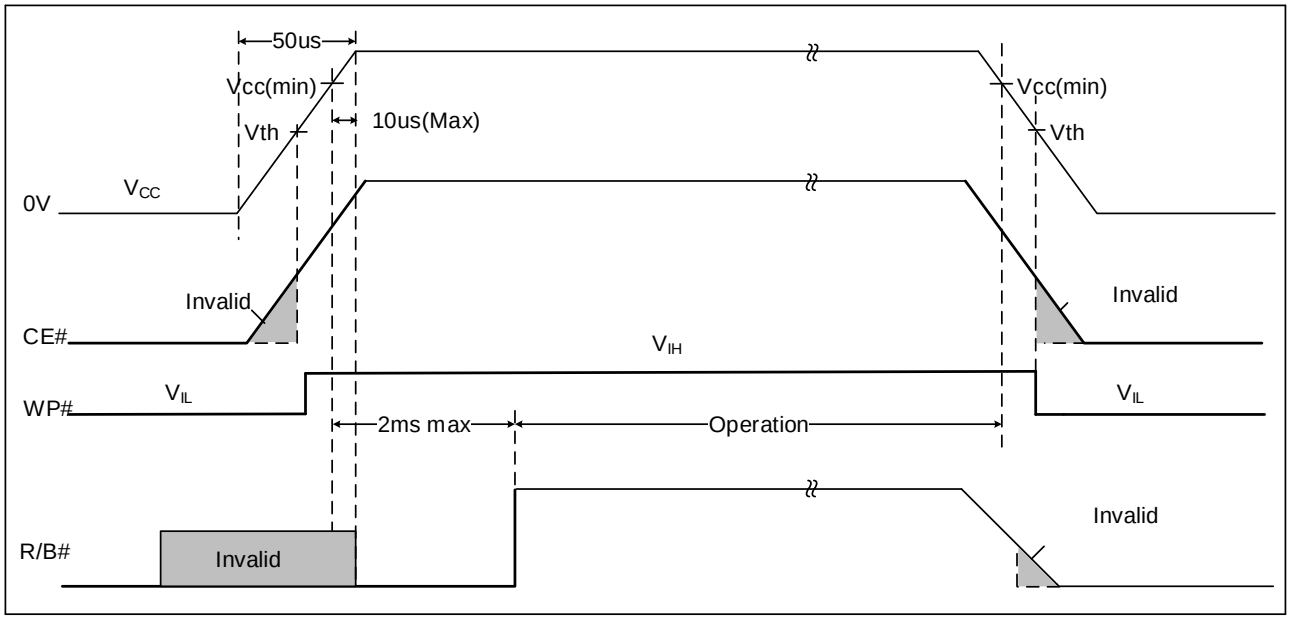
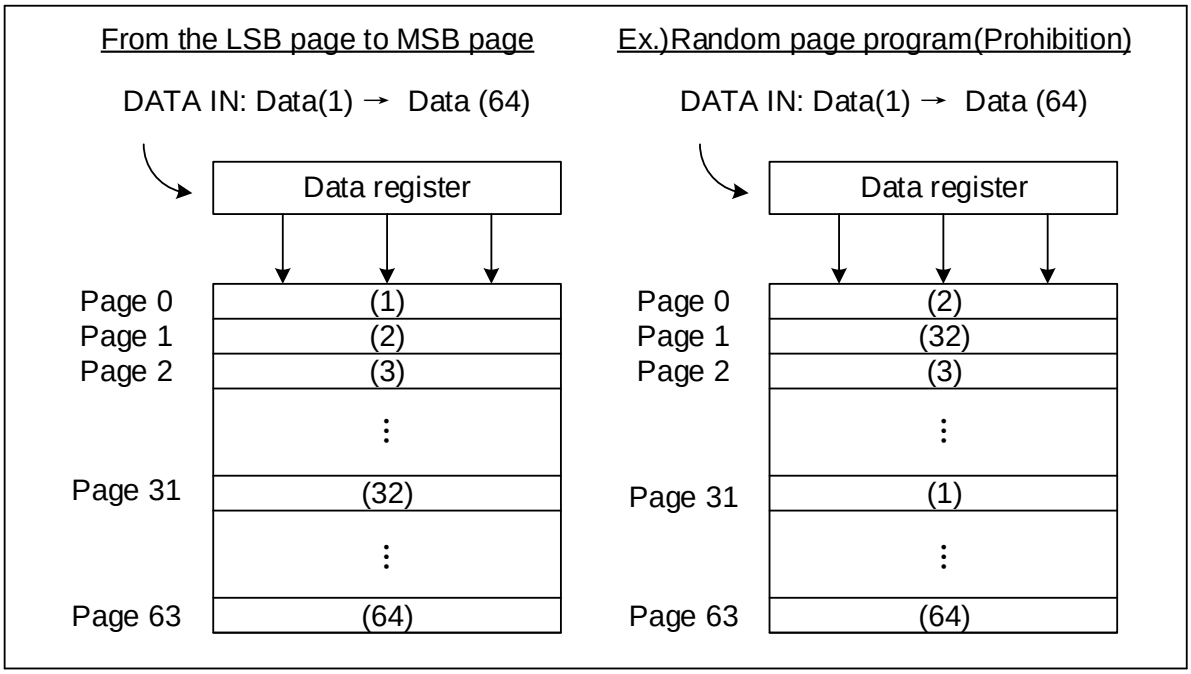


Figure 8-21: Data protection and Power on/off

Note: Vth=2.5v for 3.3V Device; Vth=1.5V for 1.8V Device

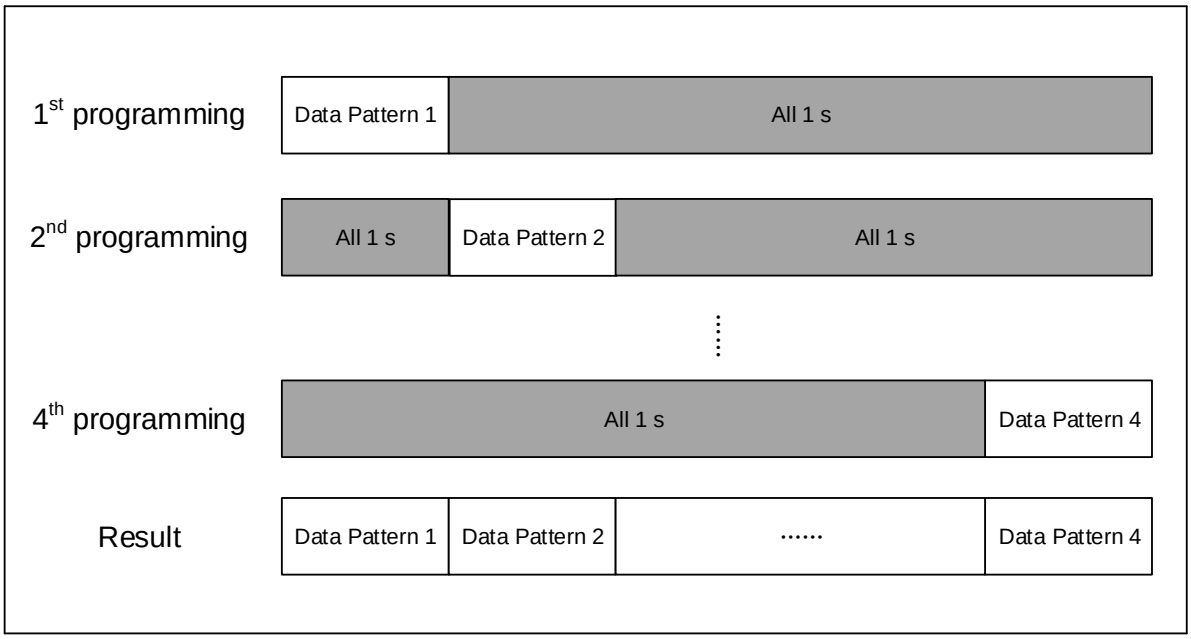
8.12 Addressing for program operation

Within a block, the pages must be programmed consecutively from the LSB (least significant bit) page of the block to MSB (most significant bit) page of the block. Random page address programming is prohibited.



8.13 Several programming cycles on the same page (Partial Page Program)

Each segment can be programmed individually as follows:



9. ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Voltage on any pin relative to VSS	VIN/OUT	-0.6 to VCC+0.4	V
	VCC(3.3V)	-0.6 to + 4.0	
	VCC(1.8V)	-0.6 to + 2.5	
Temperature Under Bias	TBIAS	-50 to +125	°C
Storage Temperature	TSTG	-65 to +150	°C

Notes:

1. Minimum DC voltage is -0.6V on input/output pins.
2. Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

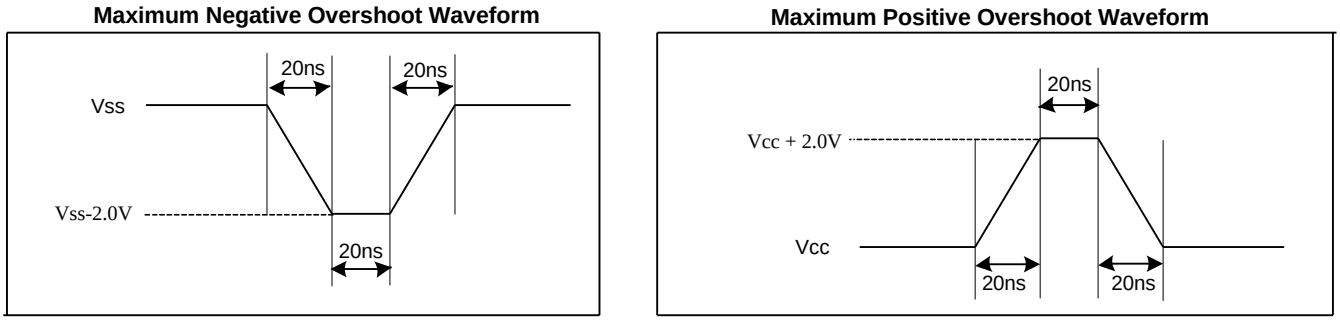


Figure 9-1. Input Test Waveform and Measurement Level

10. VALID BLOCKS

	Capacity	Min	Max	Unit
Valid Block Number	1Gb	1004	1024	Blocks

Notes:

1. The 1st block is guaranteed to be a valid block with ECC at the time of shipment.
2. Invalid blocks are one that contains one or more bad bits. The device may contain invalid blocks upon shipment.

11. DC CHARACTERISTICS

(T= -40℃~85℃, VCC=1.7~1.95V)

Parameter		Symbol	Test Conditions	1.7v ~ 1.95v			Unit
				Min	Typ.	Max	
Power on current per LUN		I_{CC0}				50	mA
Operating Current per LUN	Page Read with Serial Access	I_{CC1}	tRC=Min, CE#=V_{IL}, I_{OUT}=0mA	-	10	25	mA
	Program	I_{CC2}	-	-	10	25	
	Erase	I_{CC3}	-	-	10	25	
Standby Current (CMOS) per LUN		I_{SB}	CE#=VCC-0.2, WP#=0V/VCC	-	10	50	μA
Input Leakage Current		I_{LI}	V_{IN}=0 to VCC(max)	-	-	±10	
Output Leakage Current		I_{LO}	V_{OUT}=0 to VCC(max)	-	-	±10	
Input High Voltage		V_{IH}	-	0.8xVCC	-	VCC+0.3	V
Input Low Voltage		V_{IL}	-	-0.3	-	0.2xVCC	
Output High Voltage Level		V_{OH}	I_{OH}=-400μA	VCC-0.3	-	-	
Output Low Voltage Level		V_{OL}	I_{OL}=2.1mA	-	-	0.4	
Output Low Current(R/B#)		$I_{OL(R/B\#)}$	V_{OL}=0.4V	3	4	-	mA

(T= -40℃~85℃, VCC=2.7~3.6V)

Parameter		Symbol	Test Conditions	2.7v ~ 3.6v			Unit
				Min	Typ.	Max	
Power on current per LUN		I_{CC0}				50	mA
Operating Current per LUN	Page Read with Serial Access	I_{CC1}	tRC=Min, CE#=V_{IL}, I_{OUT}=0mA	-	15	30	mA
	Program	I_{CC2}	-	-	15	30	
	Erase	I_{CC3}	-	-	15	30	
Standby Current (CMOS) per LUN		I_{SB}	CE#=VCC-0.2, WP#=0V/VCC	-	10	50	μA
Input Leakage Current		I_{LI}	V_{IN}=0 to VCC(max)	-	-	±10	
Output Leakage Current		I_{LO}	V_{OUT}=0 to VCC(max)	-	-	±10	
Input High Voltage		V_{IH}	-	0.8xVCC	-	VCC+0.3	V
Input Low Voltage		V_{IL}	-	-0.3	-	0.2xVCC	
Output High Voltage Level		V_{OH}	I_{OH}=-400μA	VCC-0.3	-	-	
Output Low Voltage Level		V_{OL}	I_{OL}=2.1mA	-	-	0.4	
Output Low Current(R/B#)		$I_{OL(R/B\#)}$	V_{OL}=0.4V	8	10	-	mA

Note: Value guaranteed by design and/or characterization, not 100% tested in production.

12. AC CHARACTERISTICS

12.1 Test Condition

(Ta=-40 to 85°C VCC=1.7V~1.95V /2.7V~3.6V)

Parameter	GD9Fx1GF2D
Input Pulse Levels	0V to VCC
Input Rise and Fall Times	5ns
Input and Output Timing Levels	VCC/2
Output Load	1 TTL GATE and CL=30pF for 1.8v and CL=50pF for 3.3v; CL=10pF for cycle time less than 20ns.

12.2 Capacitance (TA=25°C, F=1.0MHz)

Parameter for 4Gb	Symbol	Test condition	Min	Max	Unit
Input/Output Capacitance	CI/O	V_{IL}=0V	-	6	pF
Input Capacitance	CIN	V_{IN}=0V	-	8	pF

Notes:

1. Capacitance is periodically sampled and not 100% tested.

12.3 AC Timing Characteristics

Parameter	Symbol	3.3V		1.8V		
		Min	Max	Min	Max	
CE# setup time	tCS	15	-	15	-	ns
CE# hold time	tCH	5	-	5	-	ns
CLE setup time	tCLS	10	-	10	-	ns
CLE Hold time	tCLH	5	-	5	-	ns
ALE setup time	tALS	10	-	10	-	ns
ALE hold time	tALH	5	-	5	-	ns
Data setup time	tDS	5	-	7	-	ns
Data hold time	tDH	3	-	5	-	ns
Write cycle time	tWC	12	-	20	-	ns
WE# pulse width	tWP	6	-	10	-	ns
WE# high hold time	tWH	4	-	7	-	ns
Address to data loading time	tADL	70	-	70	-	ns
WE# high to busy	tWB	-	100	-	100	ns
Ready to RE# low	tRR	20	-	20	-	ns
CLE to RE# delay	tCLR	10	-	10	-	ns
ALE to RE# delay	tAR	10	-	10	-	ns
Read cycle time	tRC	12	-	20	-	ns
RE# pulse width	tRP	6	-	10	-	ns
RE# high hold time	tREH	4	-	7	-	ns
RE# access time	tREA	-	9	-	16	ns
CE# access time	tCEA	-	25	-	25	ns
RE# high to output high Z	tRHZ	-	100	-	100	ns
CE# high to output high Z	tCHZ	-	50	-	50	ns
CE# high to output hold	tCOH	15	-	15	-	ns
RE# high to output hold	tRHOH	15	-	15	-	ns
RE# low to output hold	tRLOH	3	-	3	-	ns
Output Hi-Z to RE# Low	tIR	0	-	0	-	ns
RE# high to WE# low	tRHW	100	-	100	-	ns
WE# high to RE# low	tWHR	80	-	80	-	ns
Write protect time	tWW	100	-	100	-	ns
Feature access time	tFEAT		1		1	us
Protect busy time	tPBSY		20		20	us

Note:

1. Typical value at T_A = 25℃.
2. Value guaranteed by design and/or characterization, not 100% tested in production.

12.4 Performance Characteristics

Parameter		Symbol	Min	Typ.	Max	Unit
Data transfer from cell to register		tR			25	us
Program Time		tPROG	-	300	600	μs
Read Cache busy time		tCBSYR		5	tR	μs
Cache Program short busy time		tCBSYW		5	tPROG	μs
Number of Partial Program Cycles in the Same Page		NOP	-	-	4	cycles
Block Erase Time		tBERS	-	3	10	ms
Device resetting time	Read	tRST			5	us
	Program				10	us
	Erase				500	us

Note:

1. Typical value is measured at VCC=3.3V, TA=25℃(3.3V Device) or VCC=1.8 V, TA=25℃(1.8V Device).
2. Value guaranteed by design and/or characterization, not 100% tested in production.

13. PACKAGE INFORMATION

13.1 TSOPI-48

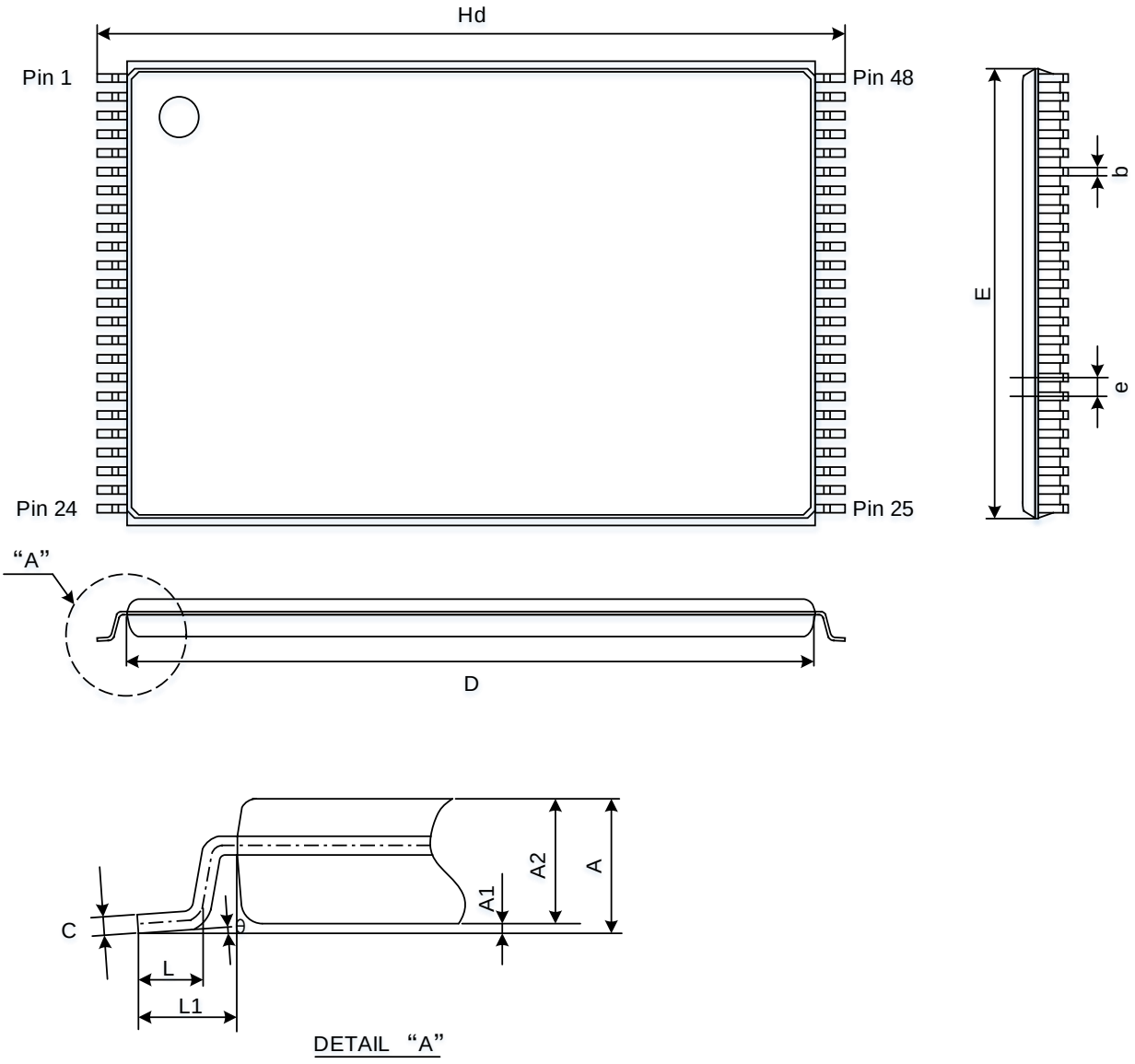


Figure 13-1: TSOPI-48 figures

Dimensions

Symbol / Unit		A	A1	A2	c	b	D	Hd	E	e	L	L1	θ
mm	Min	-	0.05	0.90	0.125	0.20	18.30	19.80	11.90	0.50	0.425	0.60	0
	Nom	-	0.10	1.00			18.40	20.00	12.00		0.525	0.80	-
	Max	1.20	0.15	1.10			18.50	20.20	12.10		0.625	1.00	7

Note：

1. Tolerance of the dimension should be ±0.1 unless otherwise specified.
2. Corner radius should be less than ±0.1R unless otherwise specified (excluding outer lead).
3. Tolerance of the angles should be ±0.5 degree unless otherwise specified.
4. The mold surface should have a finish 8±2S without luster.
   Trace of knockout pin and the ahaded portion of detail “A” should be polish surface.
5. Discrepancies between upper and lower molding cavity should be less than 0.05 of the package.
6. Mold flush should be less than 0.2mm.

13.2 FBGA-63

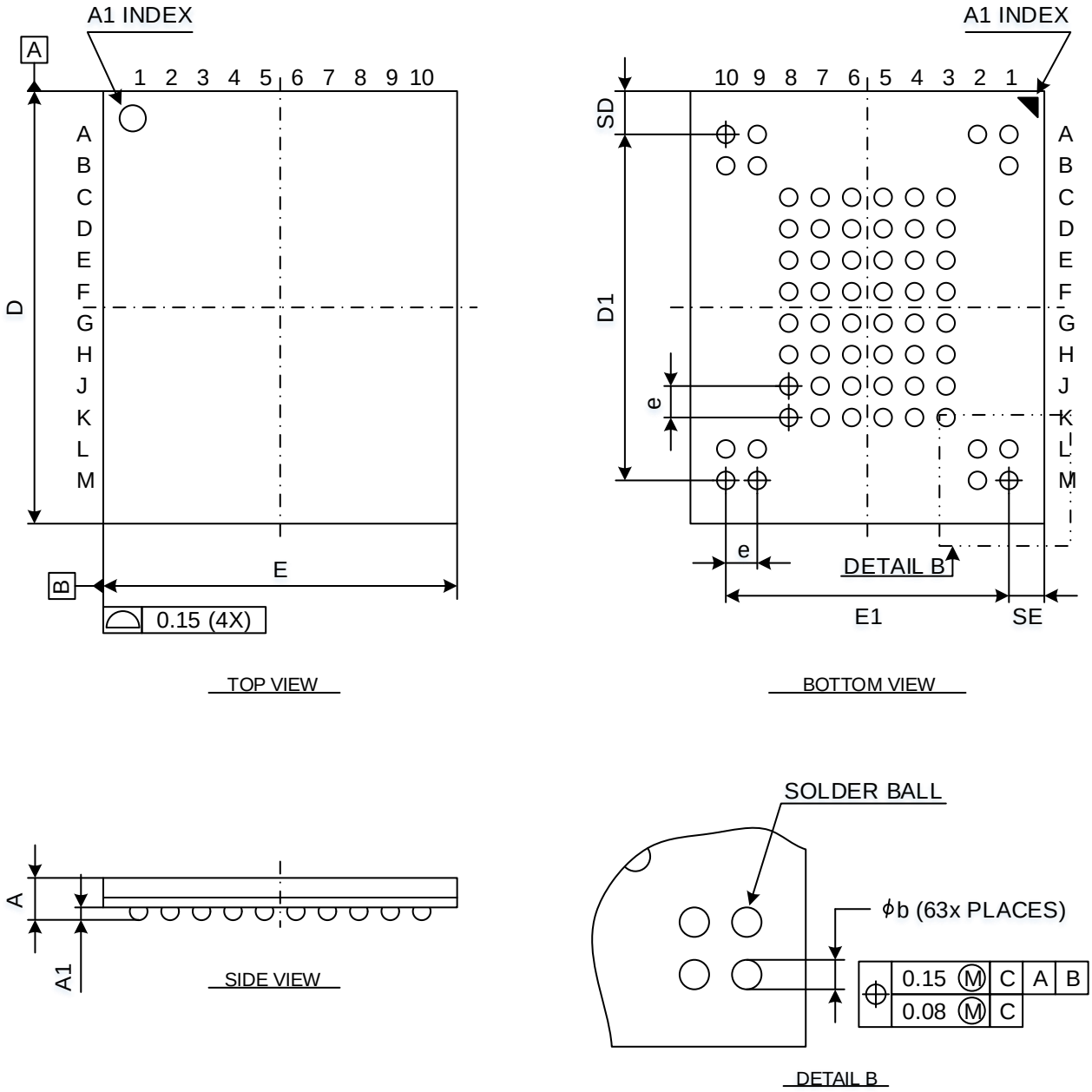


Figure 13-2: FBGA-63 figures

Dimensions

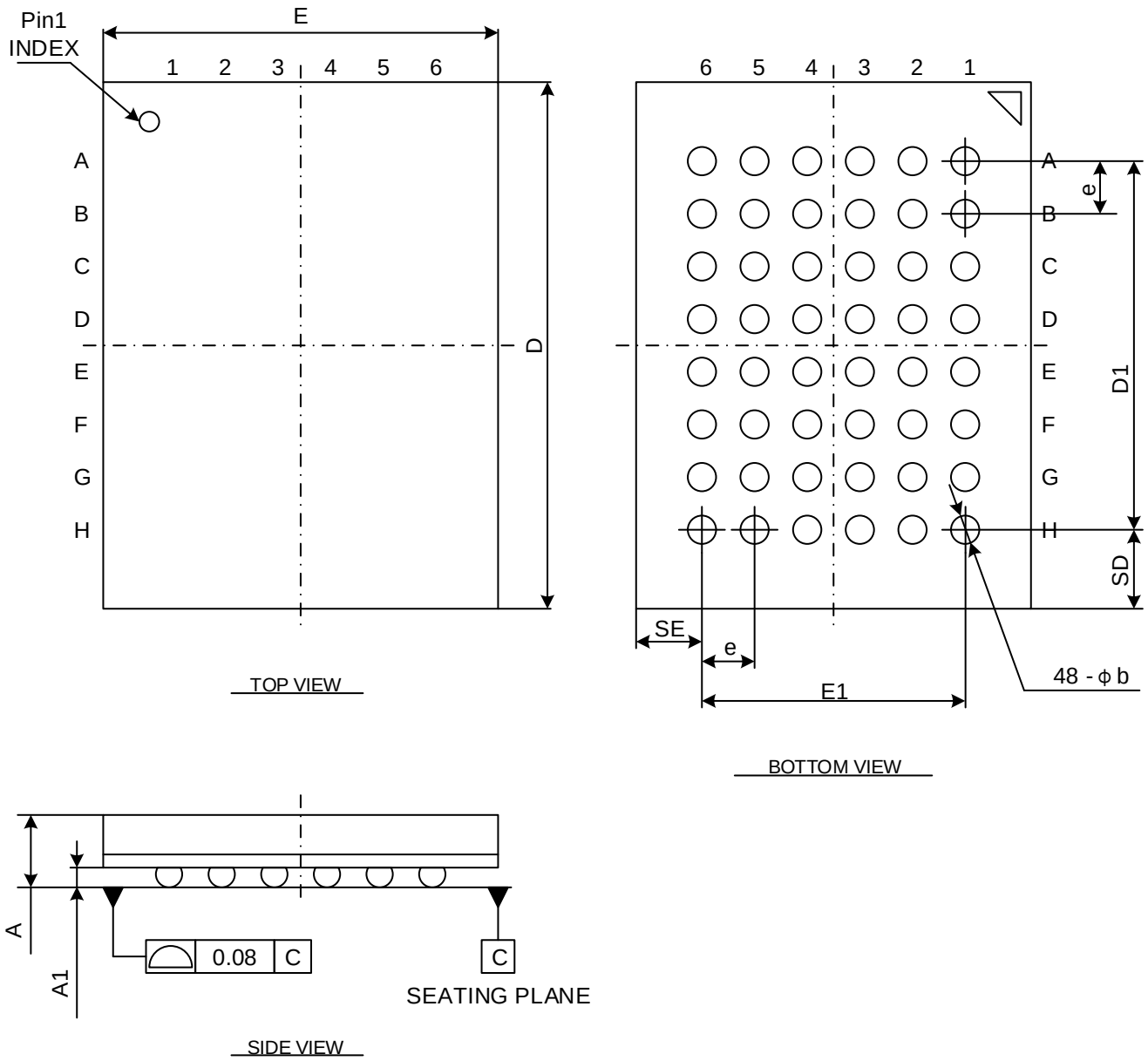
Symbol / Unit		A	A1	b	E	E1	D	D1	e	SD	SE
mm	Min	-	0.25	0.40	8.90	7.20 BSC	10.90	8.80 BSC	0.80 BSC	1.10 TYP	0.90 TYP
	Nom	-	0.30	0.45	9.00		11.00				
	Max	1.00	0.35	0.50	9.10		11.10				

Note:

1. Controlling dimension: millimeter.
2. The diameter of pre-reflow solder ball is ø0.42mm (0.40mm SMO).

13.3 FBGA-48

Figure 13-3: FBGA-48 figures



Dimensions

Symbol / Unit		A	A1	b	E	E1	D	D1	e	SD	SE
mm	Min	-	0.25	0.40	5.90	4.00 BSC	7.90	5.60 BSC	0.80 BSC	1.20 TYP	1.00 TYP
	Nom	-	0.30	0.45	6.00		8.00				
	Max	1.00	0.40	0.50	6.10		8.10				

Note：

1. Controlling dimension: millimeter.

14. Part Numbering Information

GD	9F	U	1G	8	F	2	D	M	G	I
1	2	3	4	5	6	7	8	9	10	11

1. GD

2. Memory Type

9F: Parallel NAND

3. Power Supply

	VCCQ	VCC
U	2.7v ~ 3.6v	2.7v ~ 3.6v
S	1.7v ~ 1.95v	1.7v ~ 1.95v

4. Density:

1G: 1Gb
2G: 2Gb
4G: 4Gb
8G: 8Gb

5. Organization

8: x8

6. NAND Type:

F: SLC, 1Die, 1CE#, 1R/B#
E: SLC, 2Die, 1CE#, 1R/B#
D: SLC, 4Die, 1CE#, 1R/B#

7. Function Mode:

2: Spare size is 128bytes;

8. Process Generation:

A: A GEN
B: B GEN
D: D GEN

9. Package

M: TSOPI-48
L: FBGA-63
D: FBGA-48
W: Wafer

10. Package Material & Packing

G: Lead & Halogen Free
W: Wafer

11. Temperature Grade

I: Industrial (-40C ~ 85C)

Note: (1) Industrial+: F grade has implemented additional test flows to ensure higher product quality than I grade.

15. Revision History

Version No.	History Description	Page	Date
1.0	Initial Release		2021-02-07

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